

2022.11.30 Lecture 1

13:30 – 15:00

# 量子ドット：閉じ込めと開放の物理学

Institute for Solid State Physics, University of Tokyo

Shingo Katsumoto

- 
1. 量子ドットとは，量子ドットの製法
  2. 単電子効果
  3. 量子閉じ込め効果
  4. 量子ドットを通した電気伝導

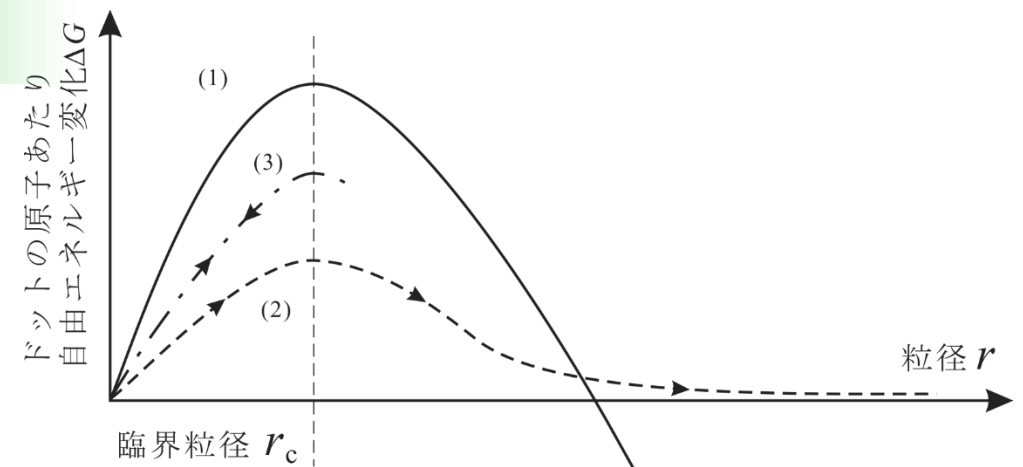
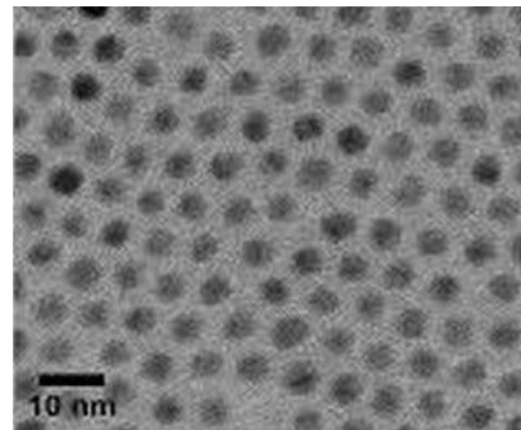
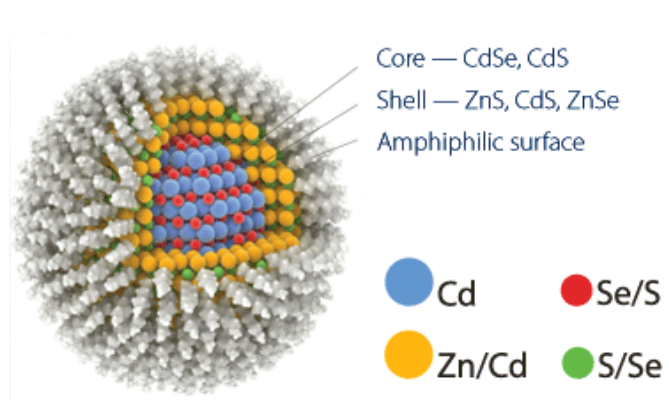
# 量子ドットとは

量子ドット (quantum dot) : 電子系を3次元的に閉じ込めたもの (0次元系)

電子系の性質による分類 { 金属量子ドット (金属超微粒子)  
半導体量子ドット

製法による分類 { 天然型 { 自己集積 真空蒸着, ガス中蒸着  
コロイド 飽和液→析出  
人工型 { 形状加工 { リソグラフィ  
やすり掛け, 機械的製法  
電氣的 金属ゲート→半導体

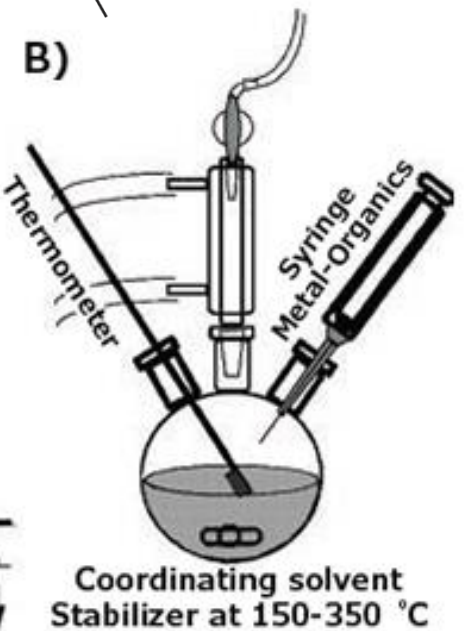
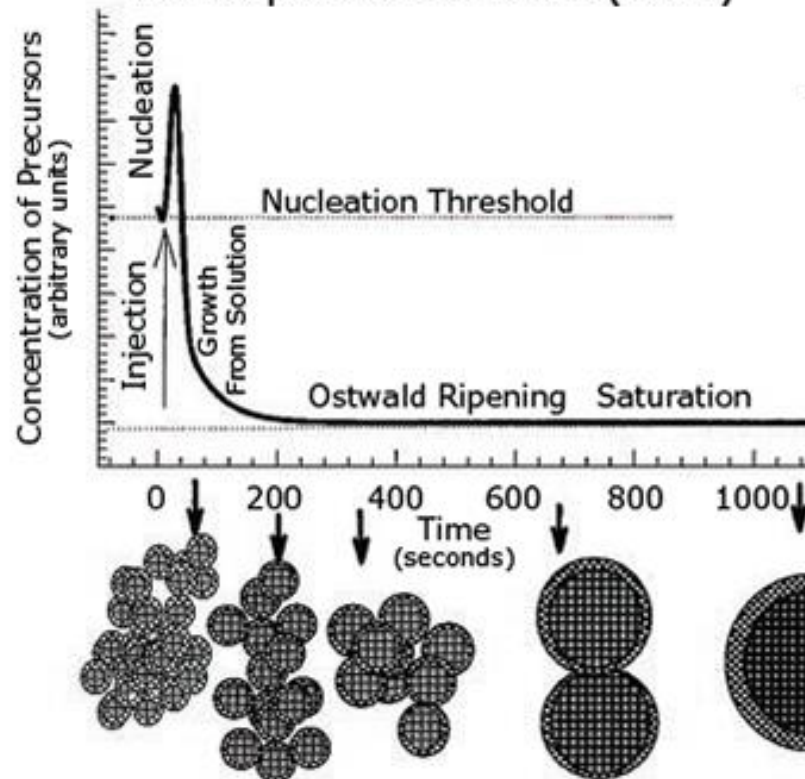
# 天然型製法の量子ドット：コロイド



コア-シェル型



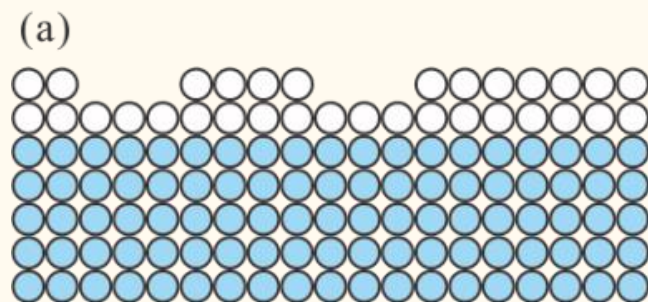
A) Monodisperse Colloid Growth (LaMer)



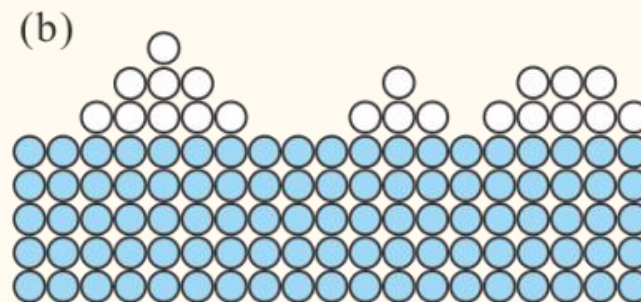
# 天然型製法の量子ドット：自己集積型

Molecular beam epitaxy (MBE) growth modes

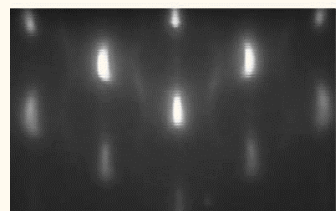
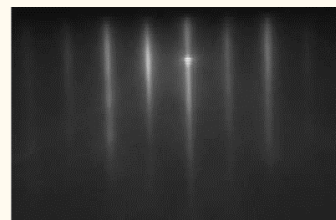
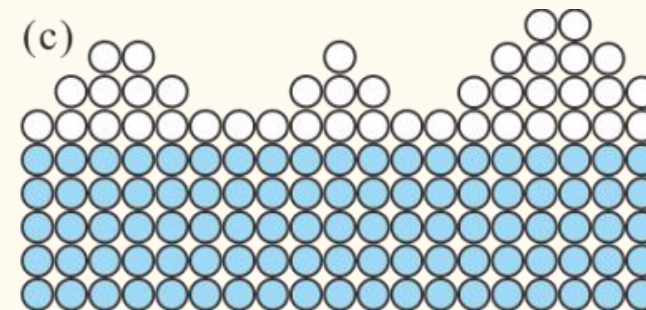
Frank-van der Merve



Volmer-Weber

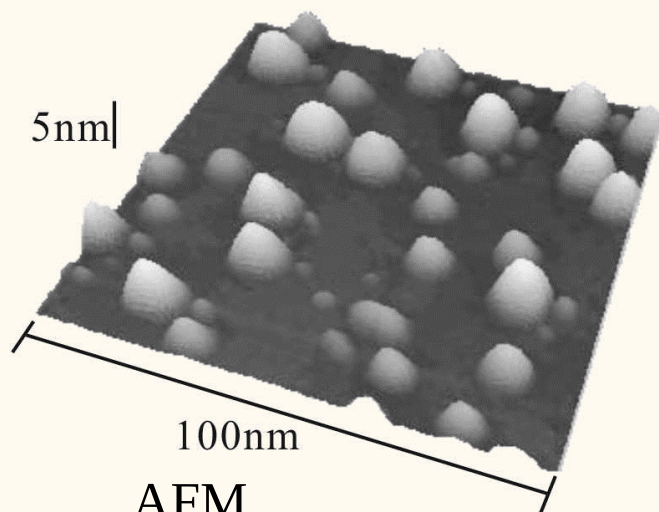


Stranski-Krastanow

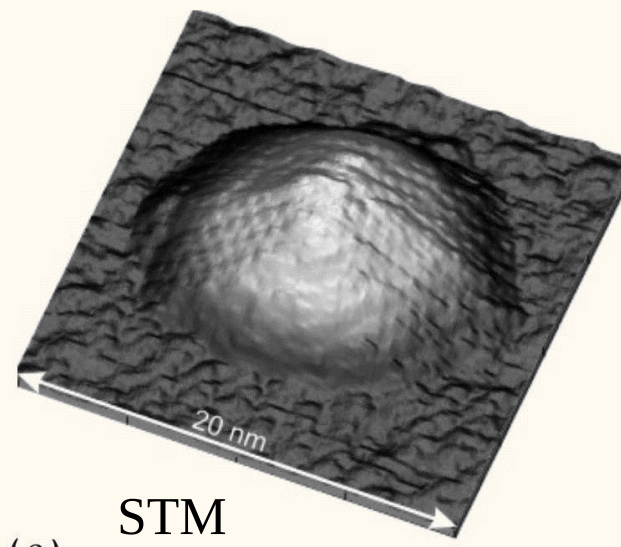


RHEED

InAs on GaAs substrate



AFM



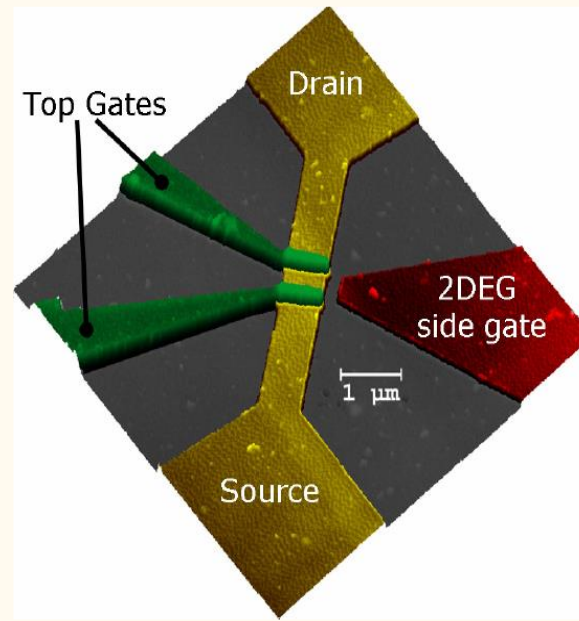
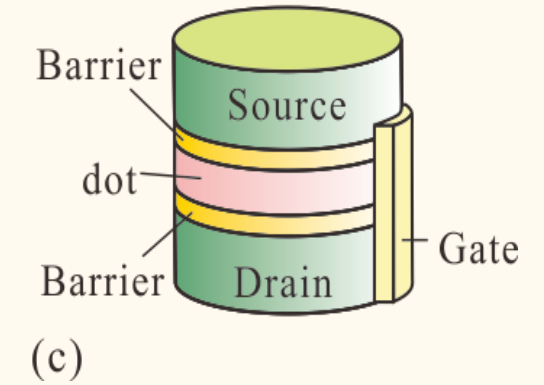
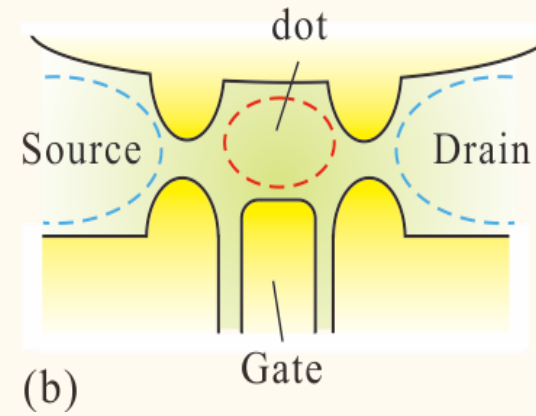
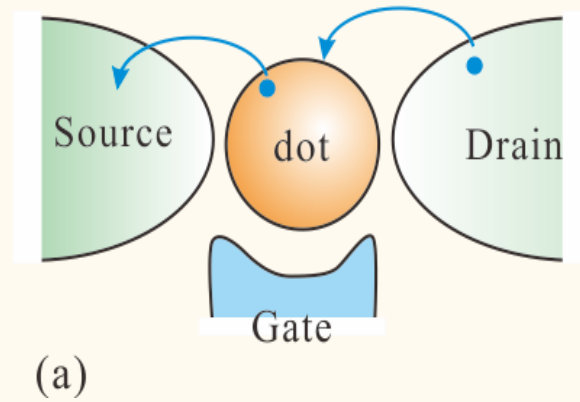
(c) STM



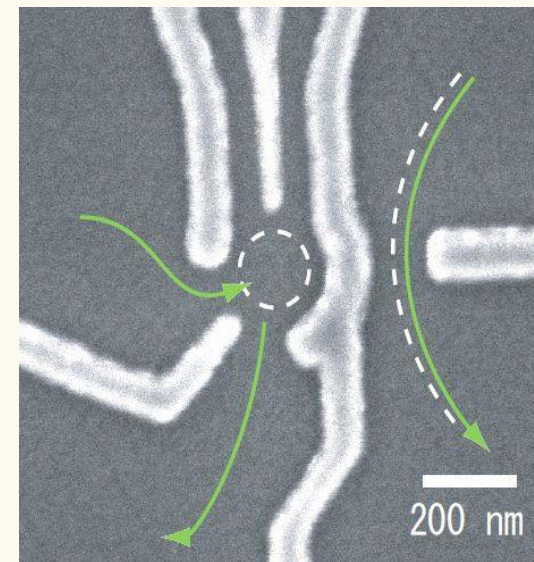
<https://www.qdlaser.com/>

# 金属ゲートを用いて形成する量子ドット

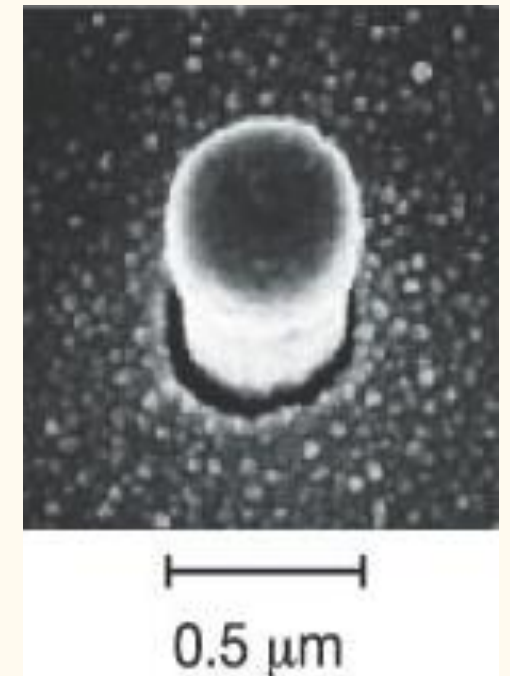
Quantum dots with  
nano-fabrication  
techniques



wrap gate



split gate  
with charge detector



vertical type

# 量子ドットの基礎

単電子効果と量子閉じ込め効果

Quantum dot + Micro LED

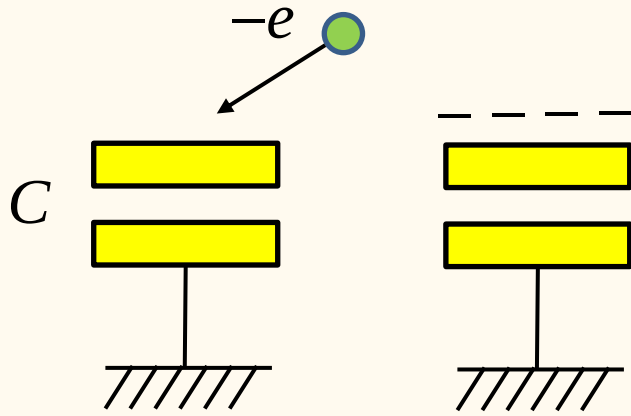
“明暗”も“色彩”もどっちも強い、新 エックスレッド XLED 登場。



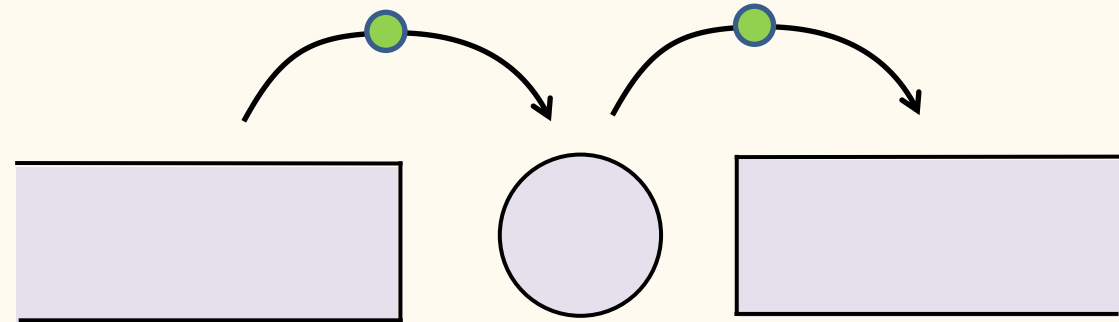
EP1

4T-C75EP1 | 4T-C70EP1  
4T-C65EP1 | 4T-C60EP1 | 4T-C55EP1

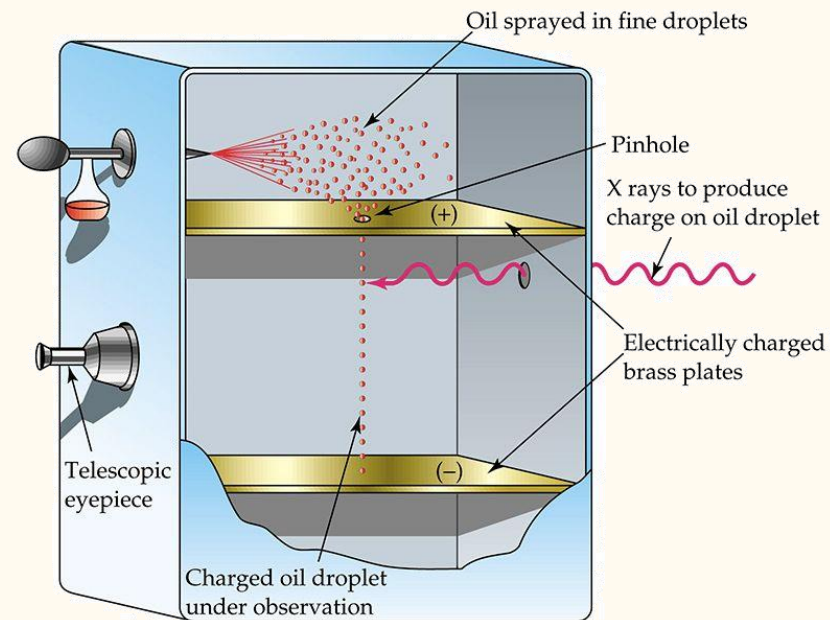
AQUOS XLED 4K

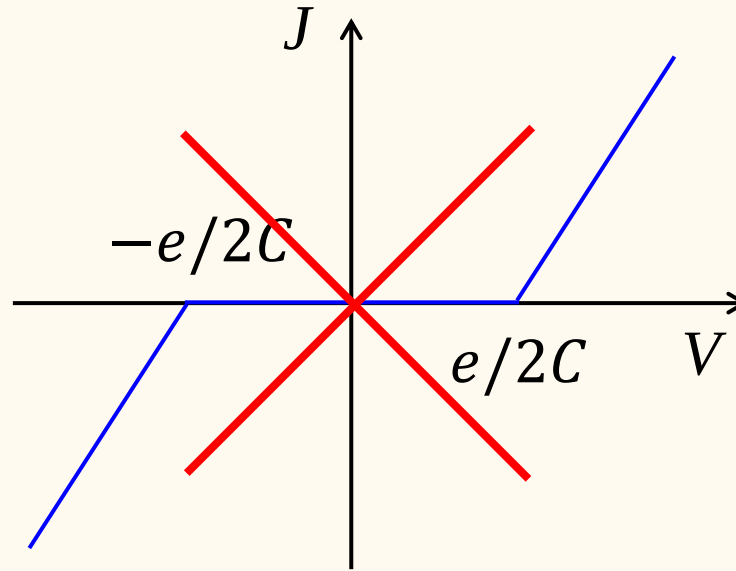
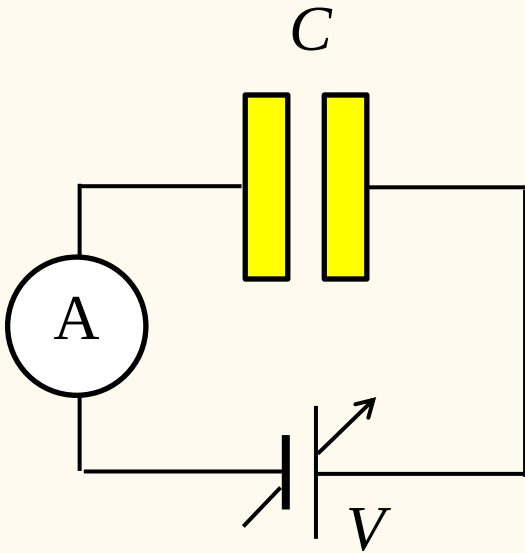


$$E_c = \frac{e^2}{2C} > k_B T \quad \text{Coulomb blockade}$$



Millikan's oil droplet experiment





Power sources: Automatically supply energy.

Energy  $\rightarrow$  Enthalpy

$$H = U - PV$$

# Constant interaction model, capacitor model

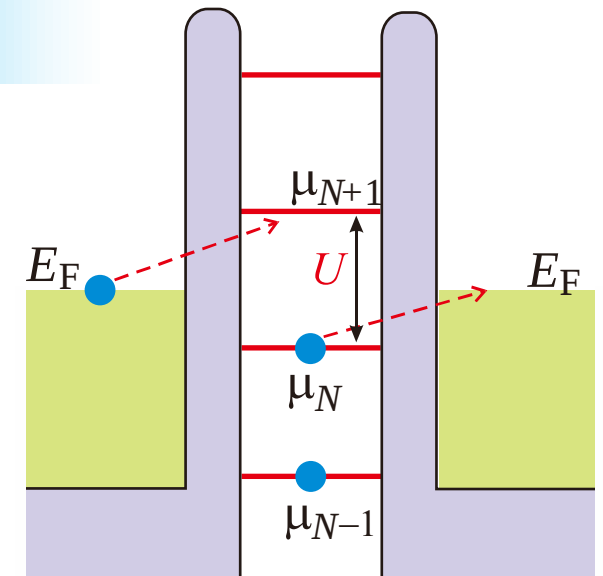
Constant interaction:  $U$

Electron number:  $N$   
Interaction energy

$$E_{cN} = {}_N C_2 U = \frac{N(N-1)U}{2} = \frac{U(N-1/2)^2}{2} - \frac{U}{8}$$

Chemical potential

$$\Delta E_+(N) = (N-1)U$$



Charge relations

$$Q_1 + Q_2 = -eN, \quad Q_1 = CV_d,$$

$$Q_2 = C_g(V_d - V_g)$$

Electrostatic energy

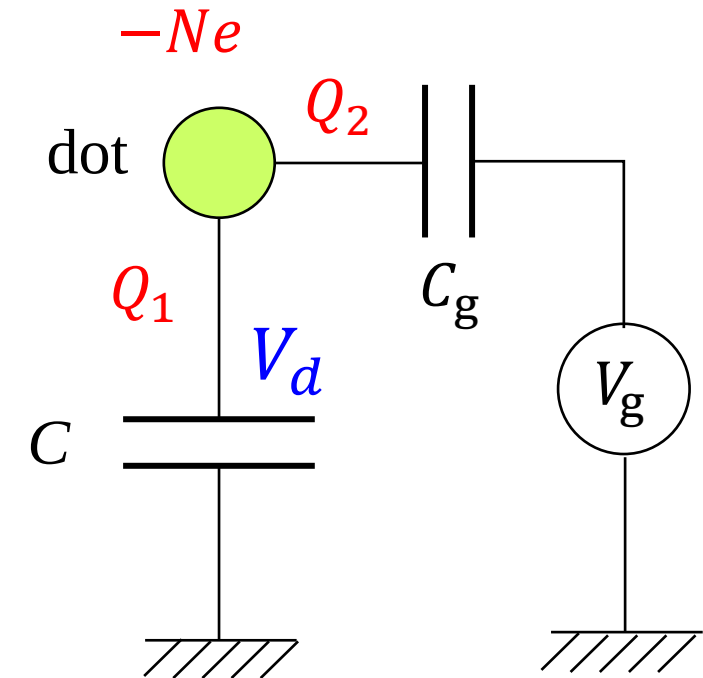
$$E = \frac{1}{2}CV_d^2 + \frac{1}{2}C_g(V_d - V_g)^2$$

Enthalpy

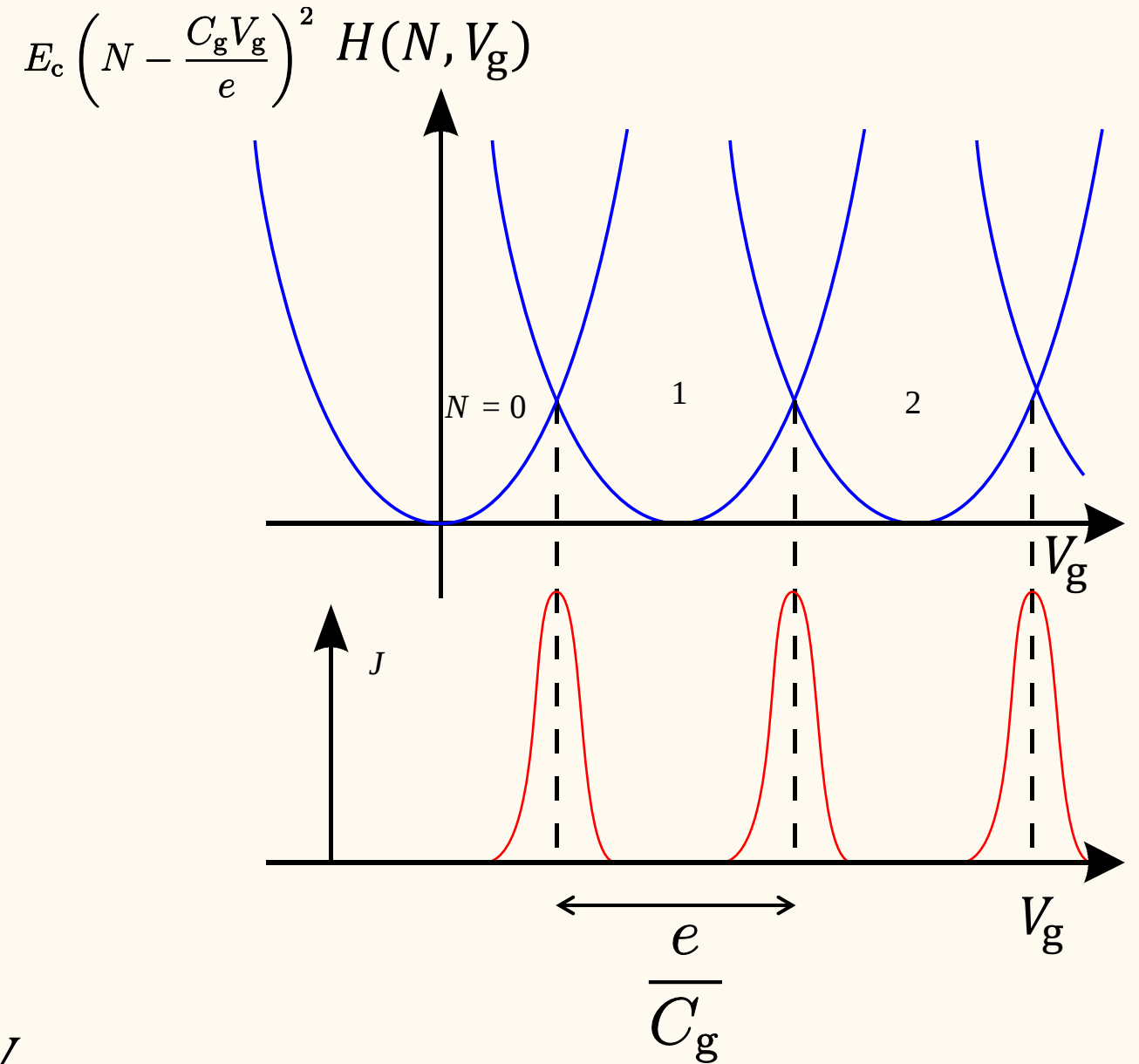
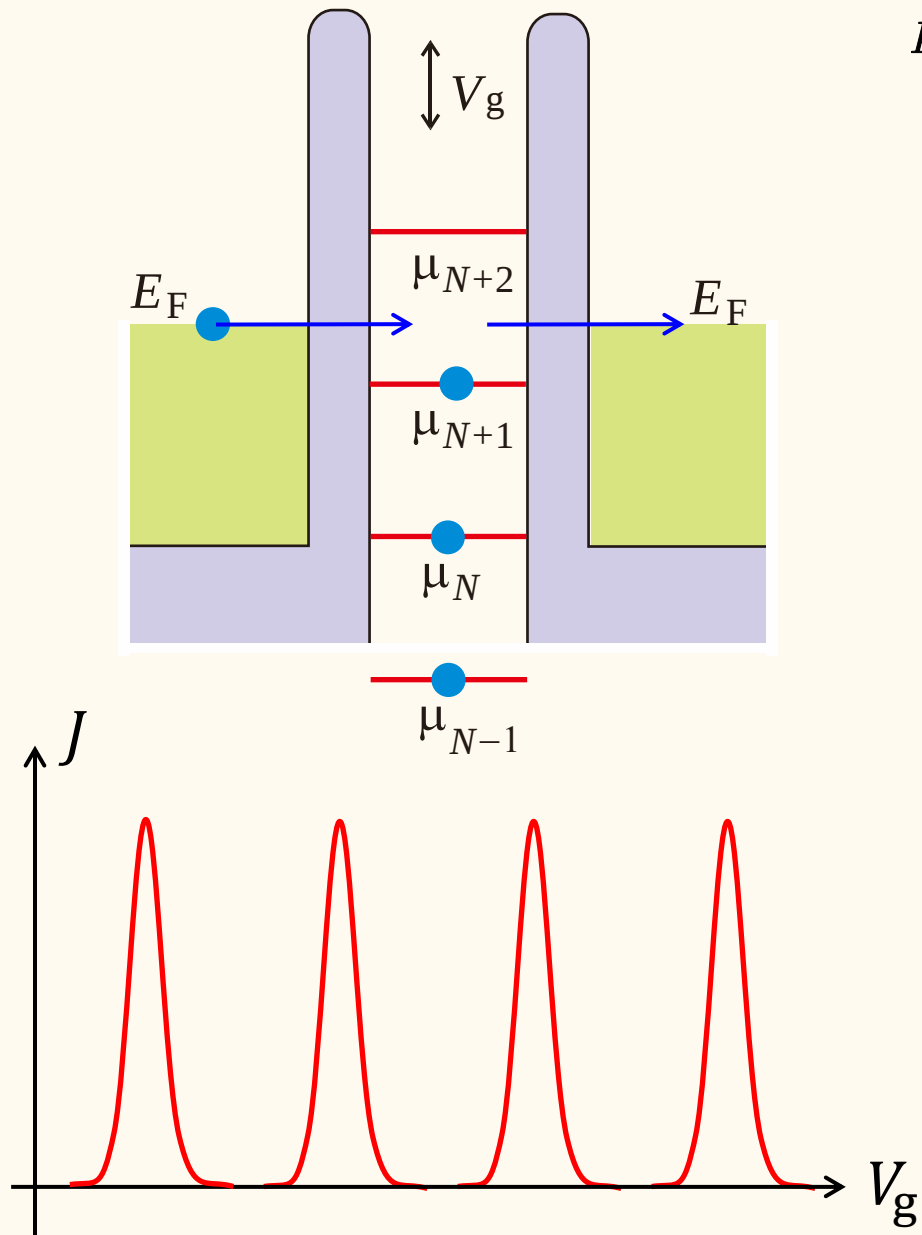
$$H(N, V_g) = \frac{(Ne - C_g V_g)^2}{2(C + C_g)} \equiv \frac{(Ne - C_g V_g)^2}{2C_s}$$

Chemical potential

$$\mu_N \approx \frac{dH}{dN} = \frac{e(Ne - C_g V_g)}{C_s} = 2E_c \left( N - \frac{C_g V_g}{e} \right)$$

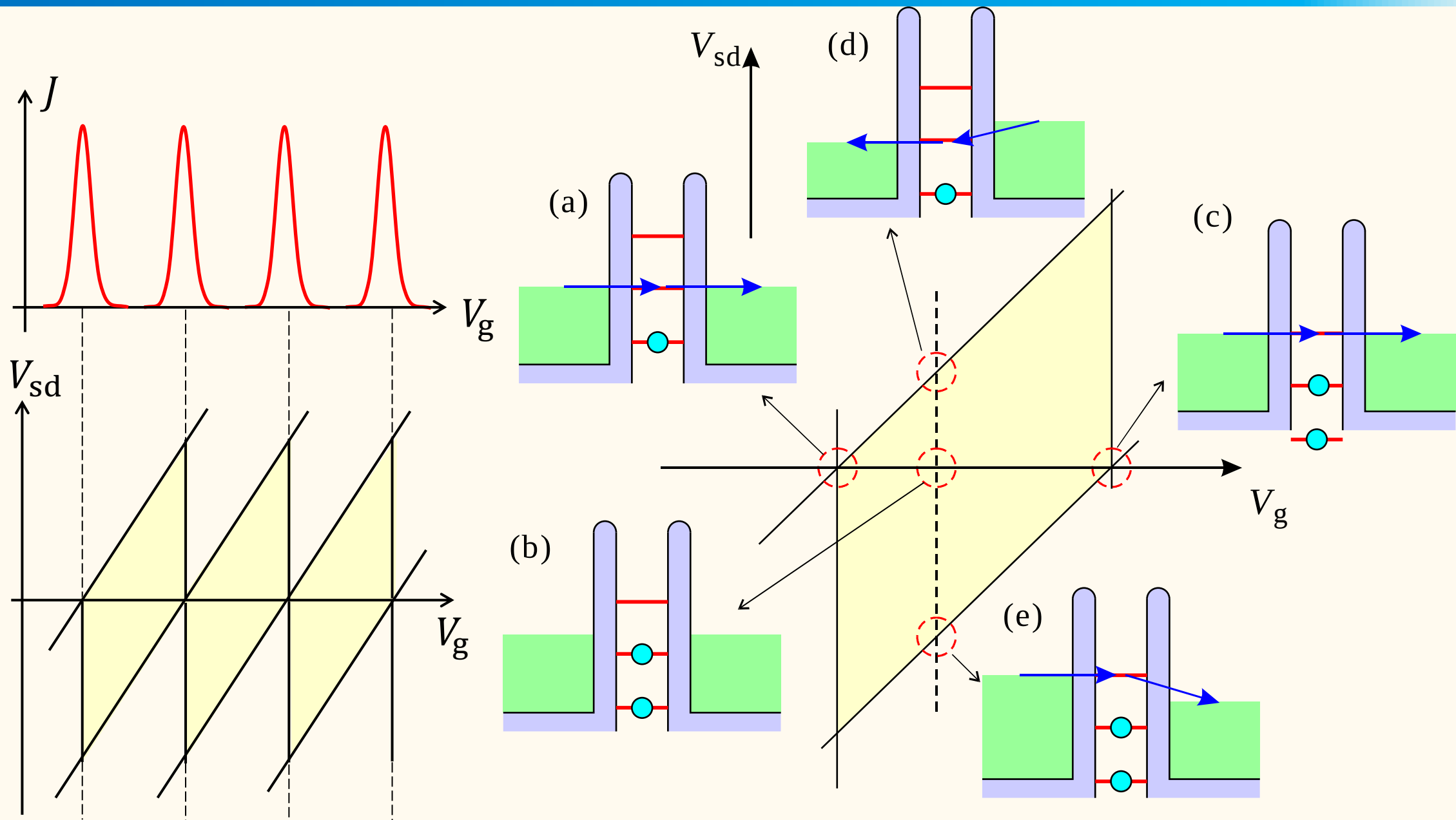


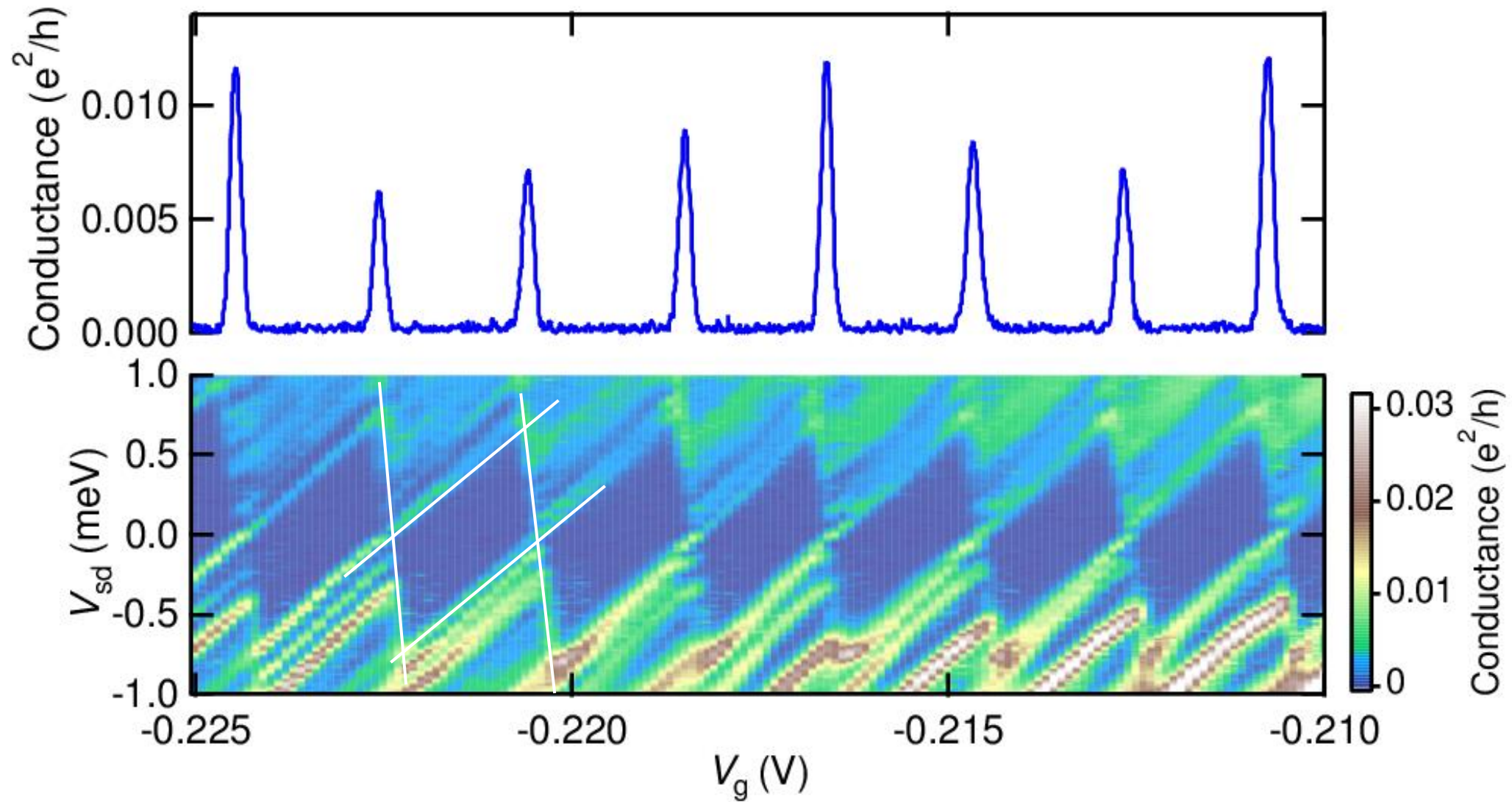
# Coulomb oscillation



# Coulomb diamond

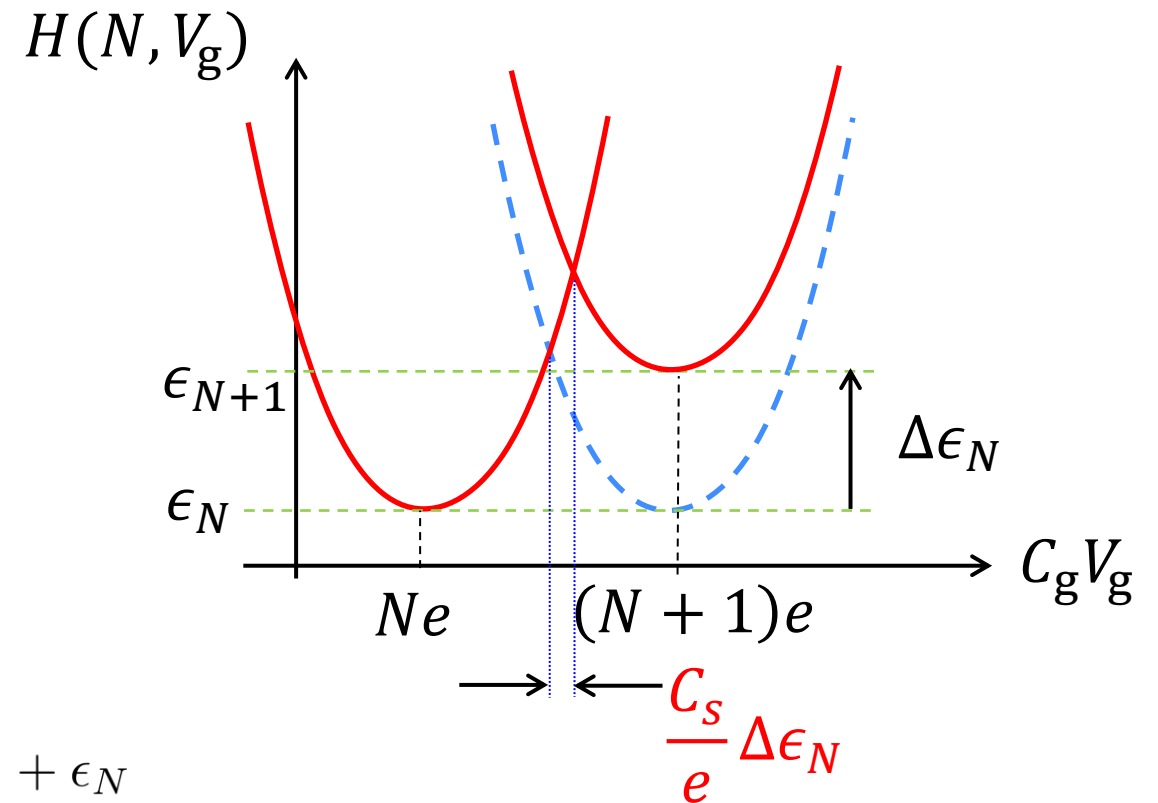
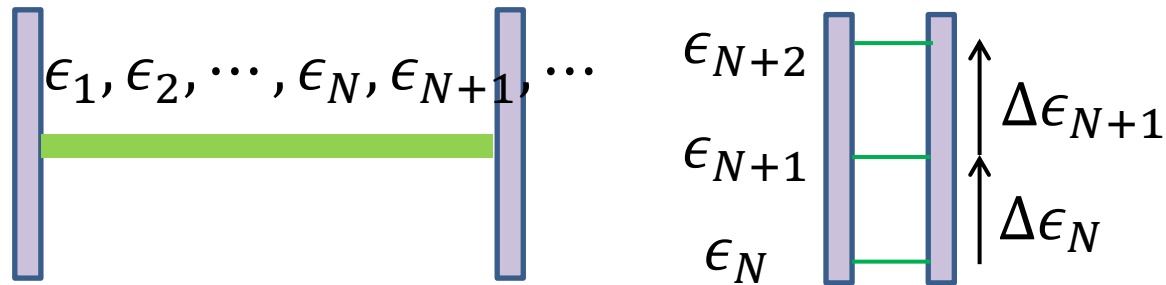
Fundamentals of quantum dots : Single electron effect





# Quantum confinement

Zero-dimensional confinement to a quantum dot gives shifts in Coulomb peak positions.



Enthalpy shift by quantum confinement

$$H(N) = \frac{(Ne - C_g V_g)^2}{2C_s} + \epsilon_N$$

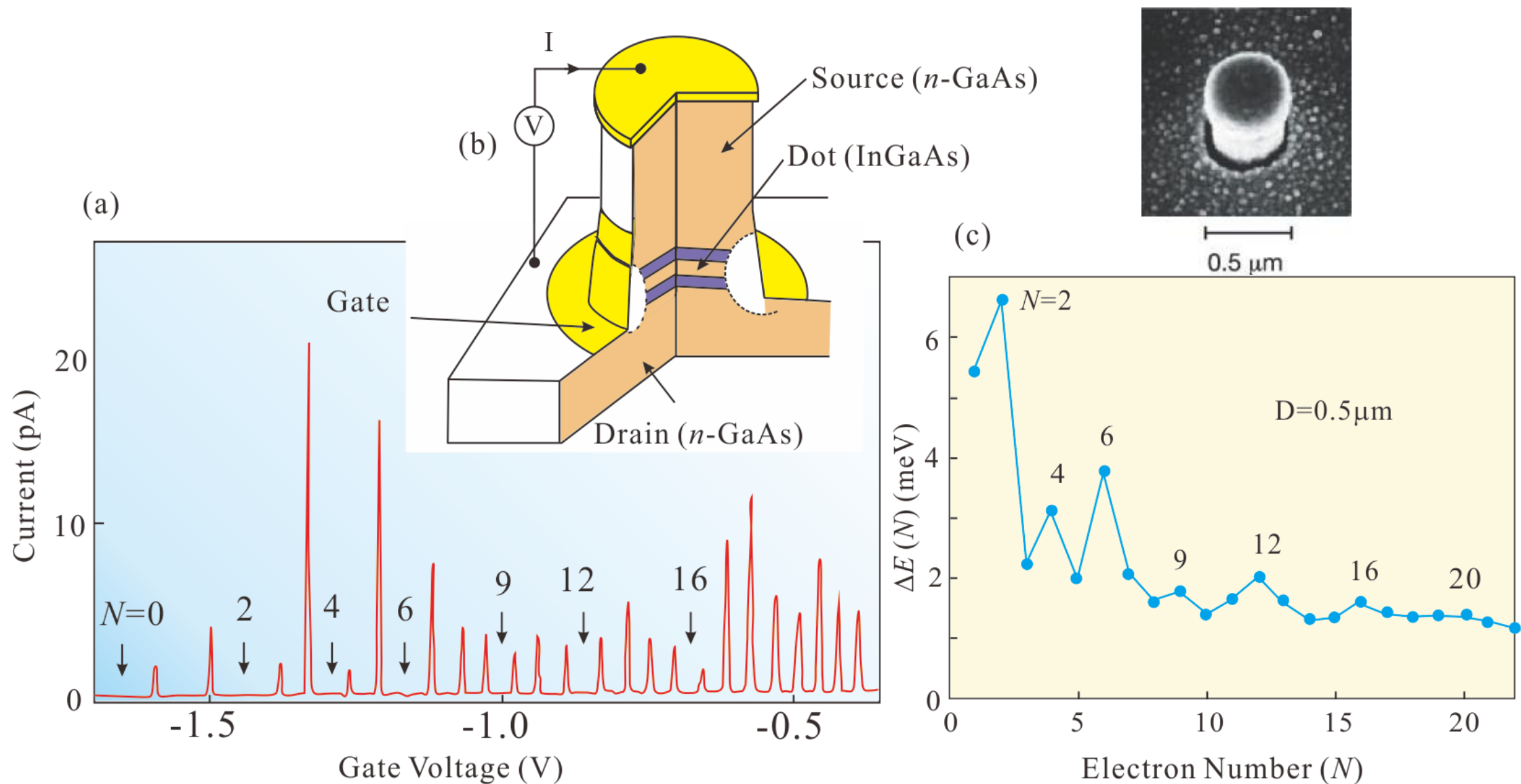
Chemical potential shift

$$\begin{aligned} \Delta H(N, N+1) &= H(N+1) - H(N) \\ &= \frac{e}{C_s} \left\{ \left( N + \frac{1}{2} \right) e - C_g V_g \right\} + \Delta \epsilon_N \\ \Delta \epsilon_N &\equiv \epsilon_{N+1} - \epsilon_N \end{aligned}$$

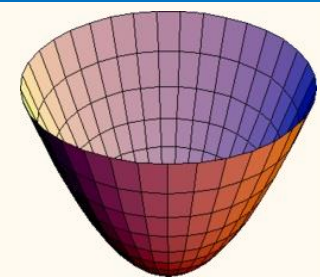
Shift in gate voltage

$$V_{gX}(N, N+1) = \frac{1}{C_g} \left\{ \left( N + \frac{1}{2} \right) e + \frac{C_s}{e} \Delta \epsilon_N \right\}$$

# Quantum confinement effect in a vertical quantum dot



# Two-dimensional harmonic potential

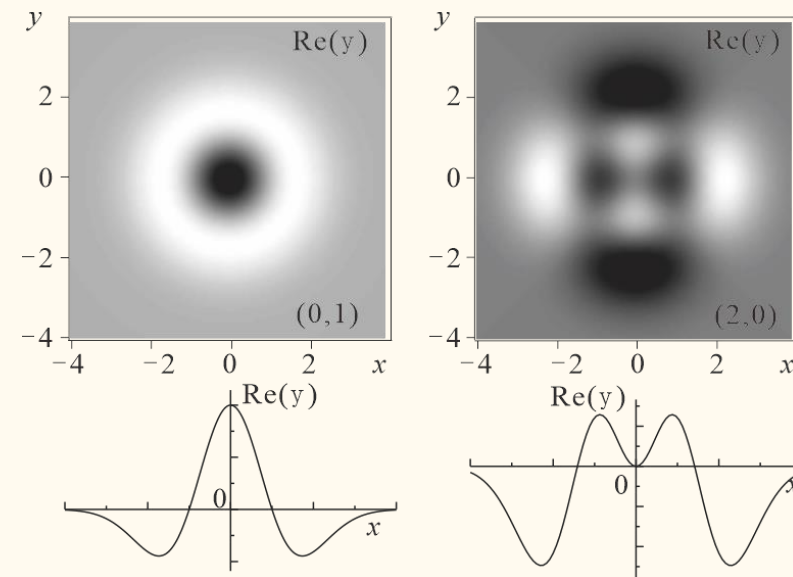
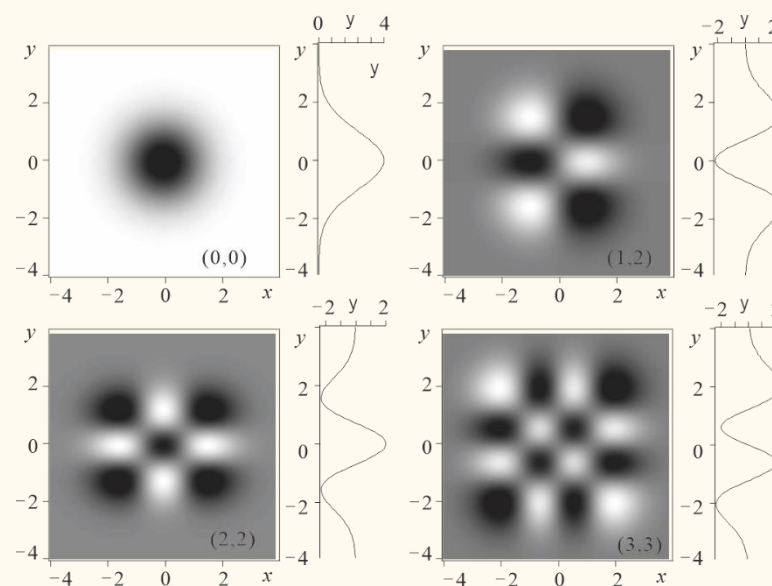
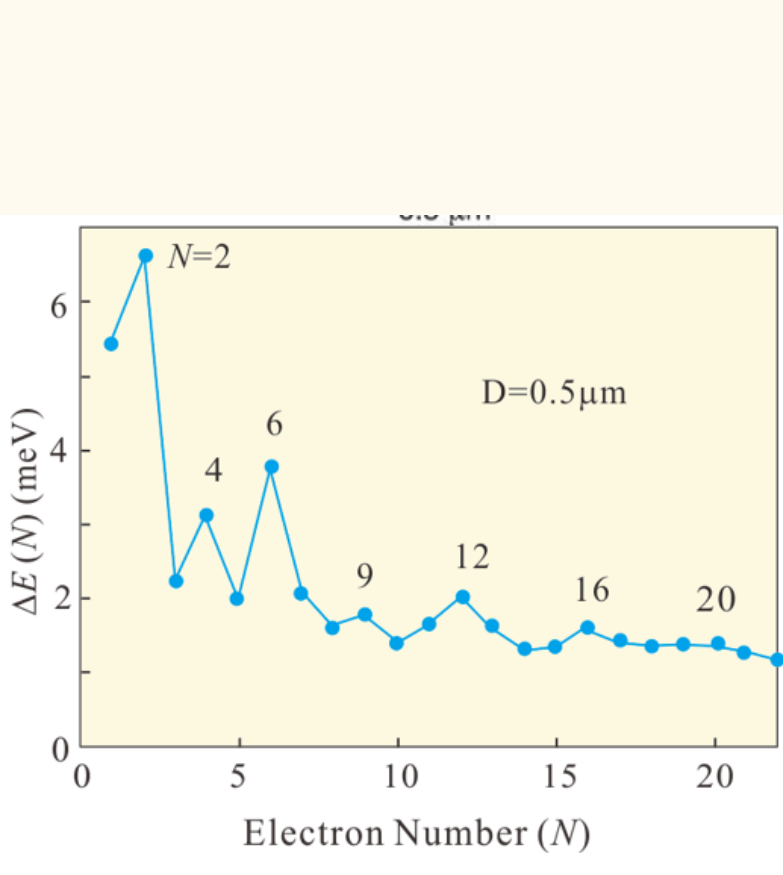


Potential shape:  $V(x, y) = \frac{m\omega}{2}(x^2 + y^2)$

Easy solutions from 1d harmonic potential

$$\psi_{n_x n_y} = A \exp \left[ -\frac{m\omega(x^2 + y^2)}{2\hbar} \right] H_{n_x} \left[ \sqrt{\frac{m\omega}{\hbar}} x \right] H_{n_y} \left[ \sqrt{\frac{m\omega}{\hbar}} y \right]$$

Eigen energies:  $E(n_x, n_y) = (n_x + n_y + 1)\hbar\omega = (n_t + 1)\hbar\omega \quad n_x + n_y \equiv n_t = 0, 1, 2, \dots$



For fixed  $n_t$   $n_x = 0, 1, 2, \dots, n_t$   $n_t + 1$  degeneracy

With spin degeneracy: 2, 4, 6, 8, ...

$$N = 2, 6, 12, 20, \dots, (n+1)(n+2), \dots$$

Hamiltonian with  $\mathbf{B} = (0,0,B)$

$$\mathcal{H} = \frac{(\mathbf{p} + e\mathbf{A})^2}{2m} + \frac{m}{2}\omega^2(x^2 + y^2) \quad \mathbf{A} = \left(-\frac{By}{2}, \frac{Bx}{2}, 0\right)$$

Expansion of the kinetic energy term

$$\begin{aligned} \frac{(\mathbf{p} + e\mathbf{A})^2}{2m} = & -\frac{\hbar^2}{2m} \left( \frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} \right) \\ & - \frac{ie\hbar B}{2m} \left( x \frac{\partial}{\partial y} - y \frac{\partial}{\partial x} \right) + \frac{e^2 B^2}{8m} (x^2 + y^2) \end{aligned}$$

Cyclotron frequency and composite harmonic confinement potential frequency

$$\omega_c = \frac{eB}{m} \quad \Omega \equiv \sqrt{\omega^2 + (\omega_c/2)^2}$$

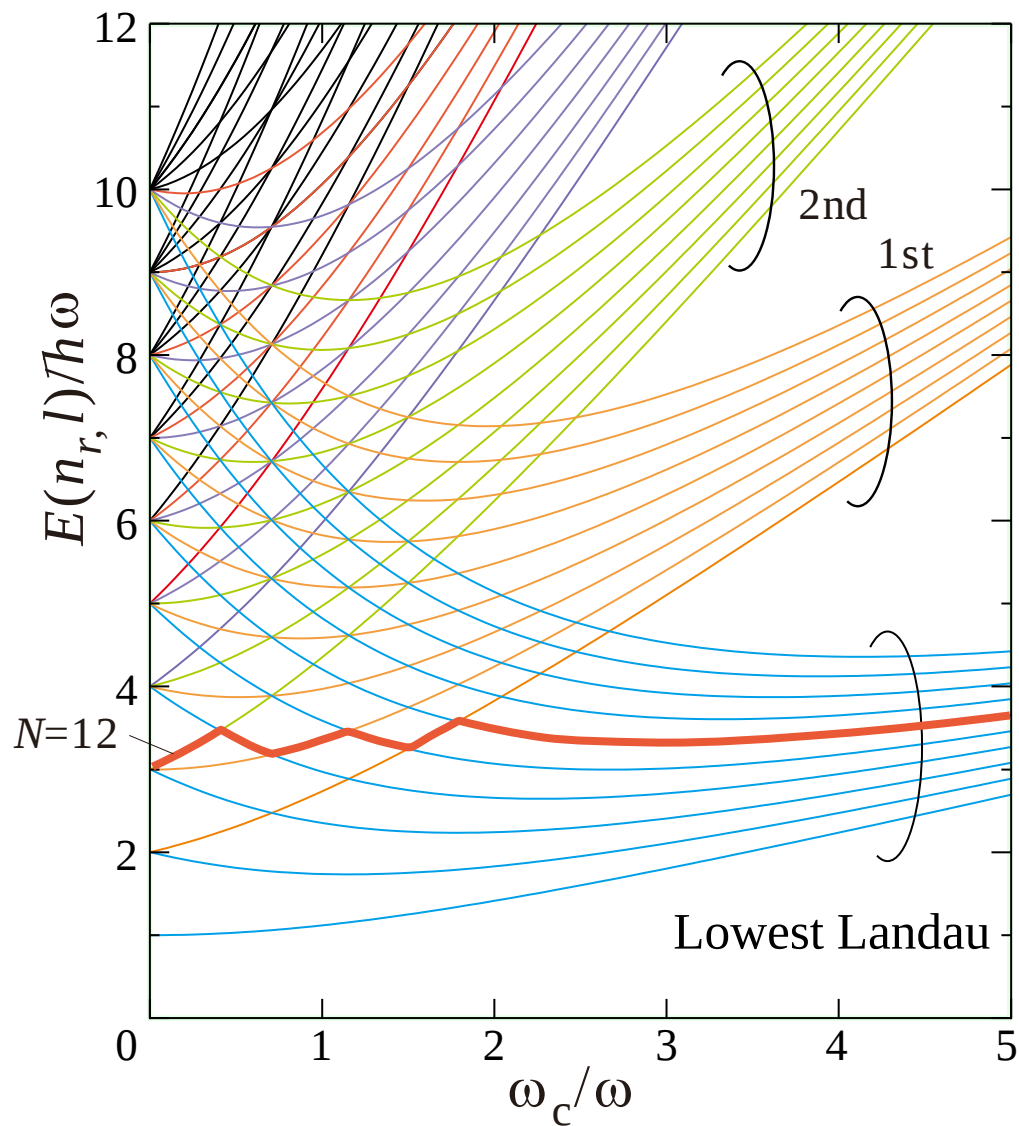
The Hamiltonian is rewritten as

$$\mathcal{H} = \frac{\hbar^2 \nabla^2}{2m} + \frac{\Omega}{2m} (x^2 + y^2) + \frac{\omega_c \hat{L}_z}{2} = \mathcal{H}_\Omega + \frac{\omega_c \hat{L}_z}{2}$$

Fock-Darwin state eigen energies

$$E(n_r, l) = \hbar\Omega(2n_r + |l| + 1) + \hbar\omega_c l/2$$

# Quantum dot in magnetic field



$$\mathcal{H} = \frac{(\mathbf{p} + e\mathbf{A})^2}{2m} + \frac{m}{2}\omega^2(x^2 + y^2) \quad \mathbf{A} = \left(-\frac{By}{2}, \frac{Bx}{2}, 0\right)$$

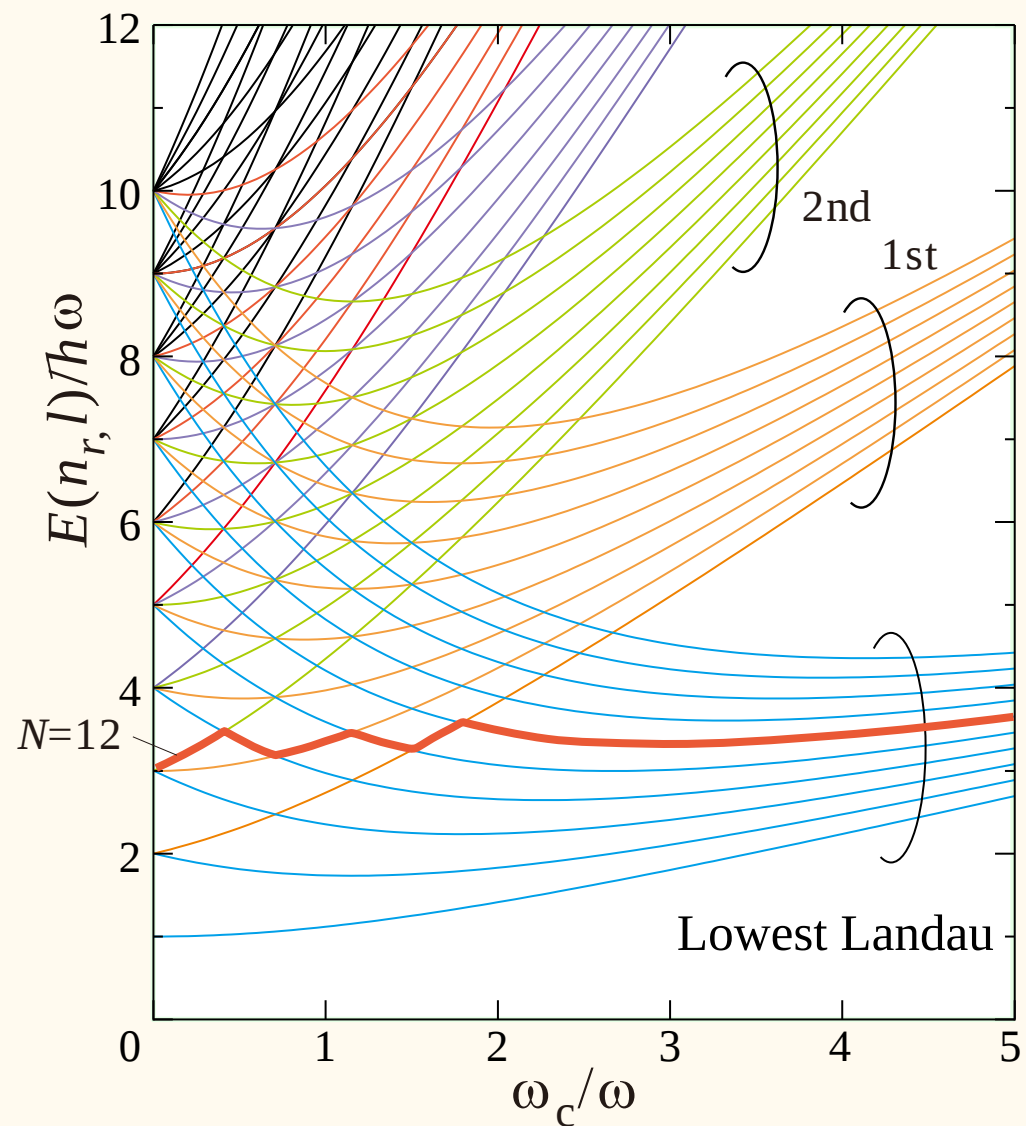
$$\begin{aligned} \frac{(\mathbf{p} + e\mathbf{A})^2}{2m} = & -\frac{\hbar^2}{2m} \left( \frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} \right) \\ & - \frac{ie\hbar B}{2m} \left( x \frac{\partial}{\partial y} - y \frac{\partial}{\partial x} \right) + \frac{e^2 B^2}{8m} (x^2 + y^2) \end{aligned}$$

$$\omega_c = \frac{eB}{m} \quad \Omega \equiv \sqrt{\omega^2 + (\omega_c/2)^2}$$

$$\mathcal{H} = \frac{\hbar^2 \nabla^2}{2m} + \frac{\Omega}{2m} (x^2 + y^2) + \frac{\omega_c \hat{L}_z}{2} = \mathcal{H}_\Omega + \frac{\omega_c \hat{L}_z}{2}$$

$$E(n_r, l) = \hbar\Omega(2n_r + |l| + 1) + \hbar\omega_c l/2$$

# Fock-Darwin states

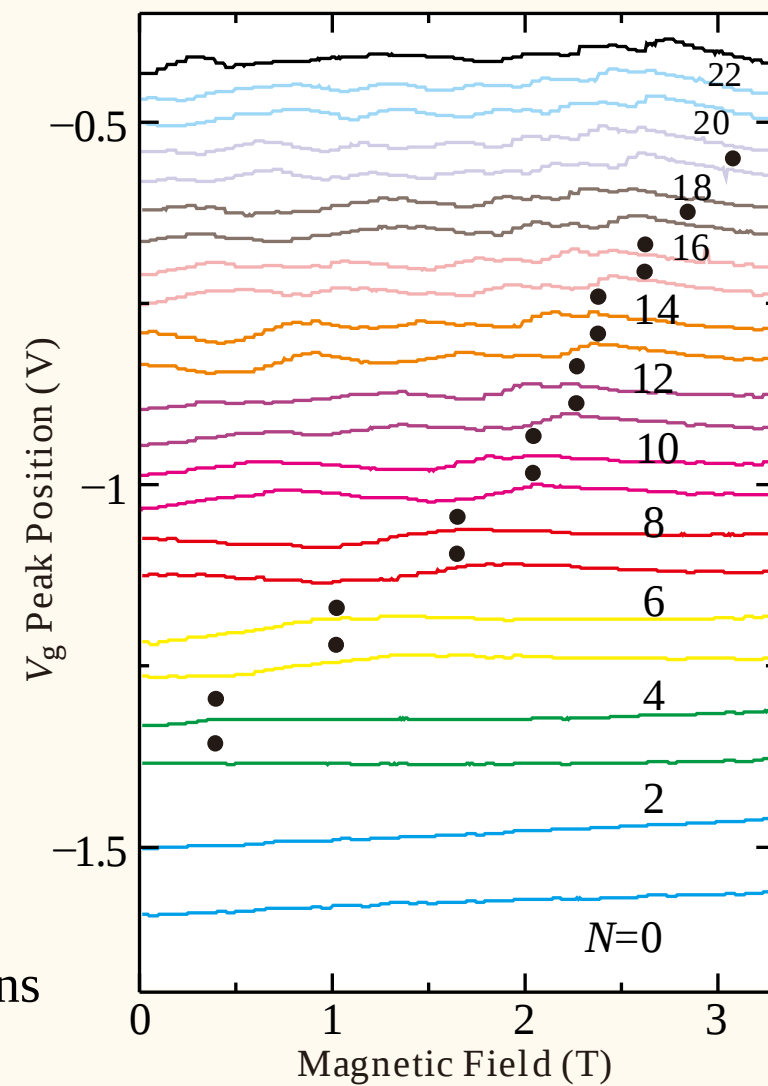


Level crossing points

$$\left(\frac{\omega_c}{\omega}\right)^2 = n_L - 2 + \frac{1}{n_L}$$

$n_L$ : Landau index  
= 1, 2, ....

• : Solutions



Fundamentals of quantum dots

# Transport through quantum dots

Quantum confinement

Cascade connection of T-matrices

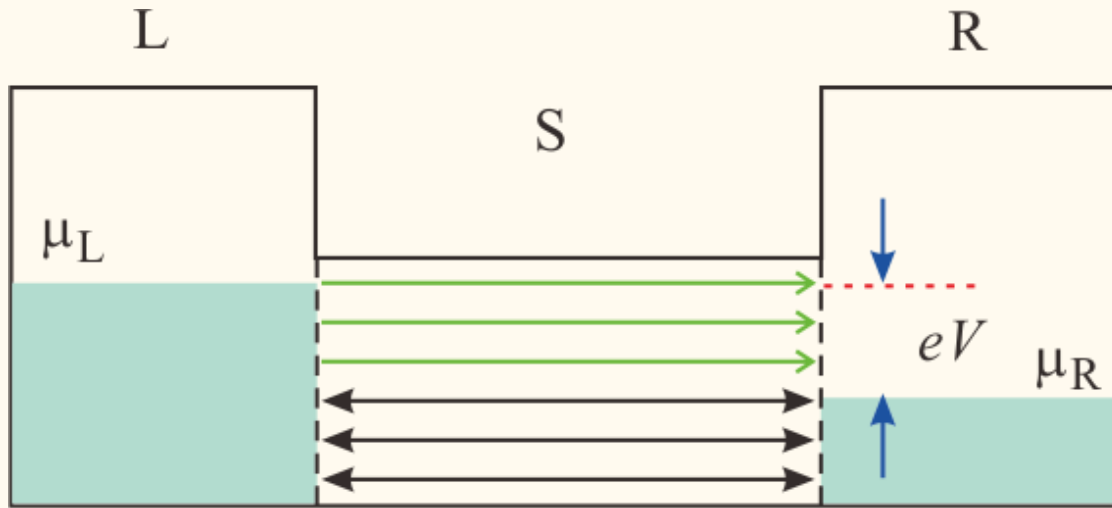
Single electron

Master equation



## Transport through a 1d wire without scattering

Landauer, IBM Res. Dev. **1**, 223 (1957)



L, R : Particle reservoirs

Thermal equilibrium:  
well defined chemical potentials

Instantaneous thermalization:  
particles loose quantum coherence

$$j(k) = \frac{e}{L} v_g = \frac{e}{\hbar L} \frac{dE(k)}{dk}$$

$L$ : wavefunction normalization length

$$J = \int_{k_R}^{k_L} j(k) \frac{L}{2\pi} dk = \frac{e}{h} \int_{\mu_R}^{\mu_L} dE = \frac{e}{h} (\mu_L - \mu_R) = \frac{e^2}{h} V$$

$$G = \frac{J}{V} = \frac{e^2}{h} \equiv G_q \quad \text{Conductance quantum} \quad \left( \frac{2e^2}{h} \equiv G_q \quad \text{spin freedom} \right)$$

# Conductance quantum as uncertainty relation

## Space coordinate-wavenumber

Wave packet:  $\Delta k \rightarrow \Delta x = \frac{2\pi}{\Delta k}, \quad v_g = \frac{\Delta E}{\hbar \Delta k}$

Fermion statistics: electron charge concentration =  $\frac{e}{\Delta x} = \frac{e \Delta k}{2\pi}$

$$J = e n_{\text{electron}} v_g = \frac{e}{\Delta x} \frac{\Delta E}{\hbar \Delta k} = \frac{e^2}{h} V$$

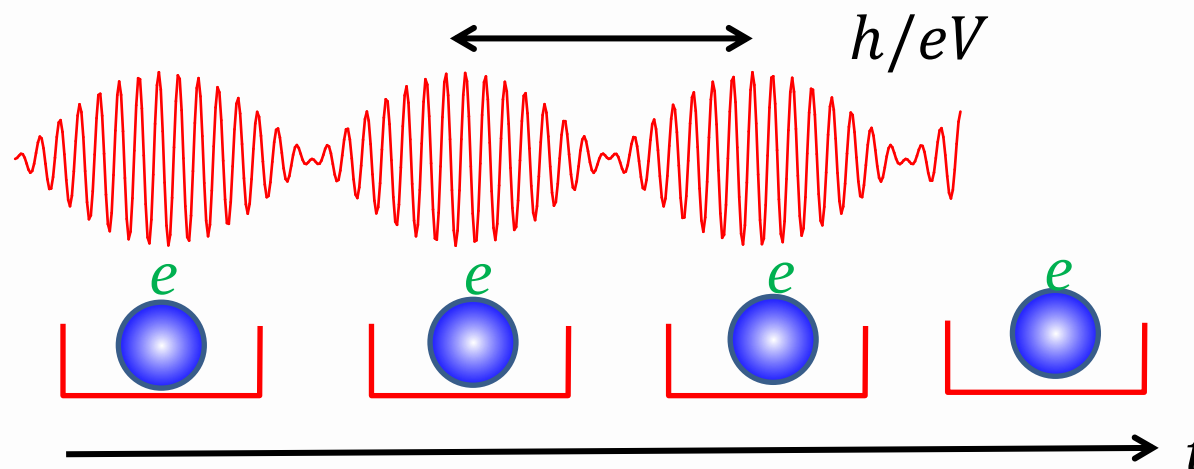
## Energy-time

Energy width:  $\Delta E = eV$

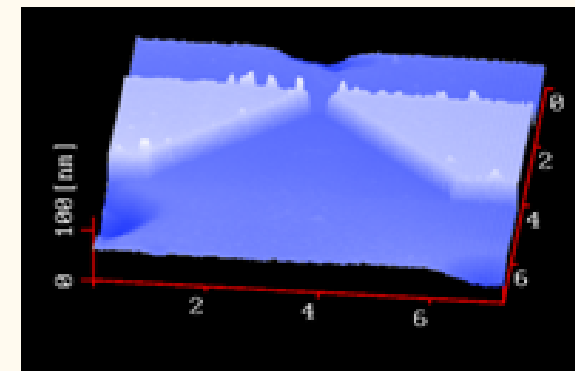
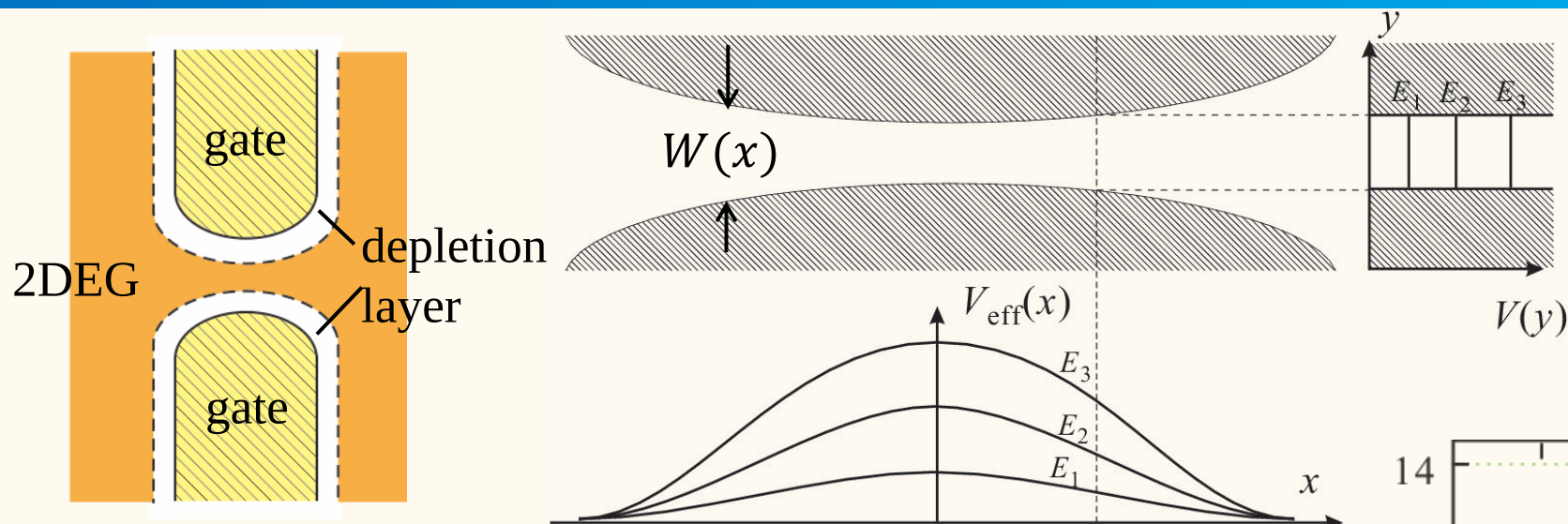
Wave packet width in time:  $\Delta t = \frac{h}{\Delta E} = \frac{h}{eV}$

Fermion anti-bunching effect:  $J = \frac{e}{\Delta t} = \frac{e^2}{h} V$

Conductance quantum comes from fermion statistics of electrons

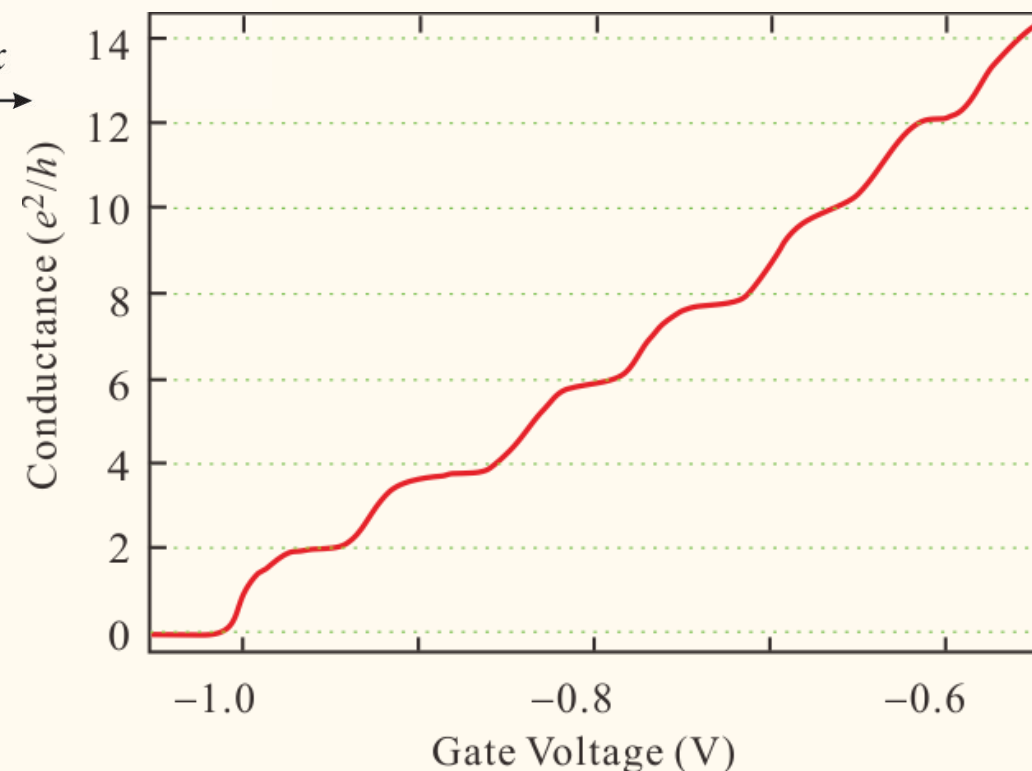


# Landauer formula: multipath and quantum point contact (QPC)



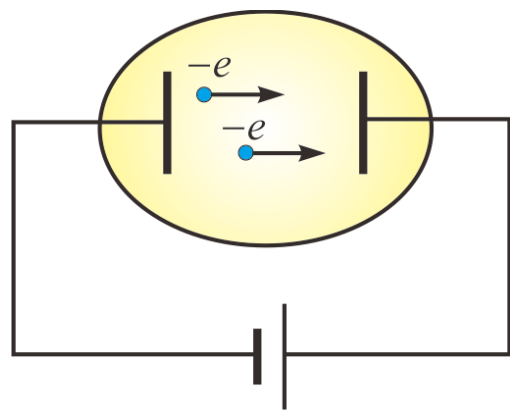
$$\begin{aligned}
 H\psi(x, y) &= \frac{\hbar^2}{2m} \left( \frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} \right) \varphi_n(y) \phi(x) \\
 &= \varphi_n(y) \frac{\hbar^2}{2m} \left( \frac{\partial^2}{\partial x^2} + \left( \frac{n\pi}{2W} \right)^2 \right) \phi(x) = E \varphi_n(y) \phi(x) \\
 V_{\text{eff}}(n, x) &= \frac{\hbar^2}{2m} \left( \frac{n\pi}{2W(x)} \right)^2
 \end{aligned}$$

Transmissible one-dimensional system: **Conductance Channel**



Sensitivity to gate voltage → used as a **remote charge (single electron) sensor**

# Shot noise reduction on the conductance plateaus



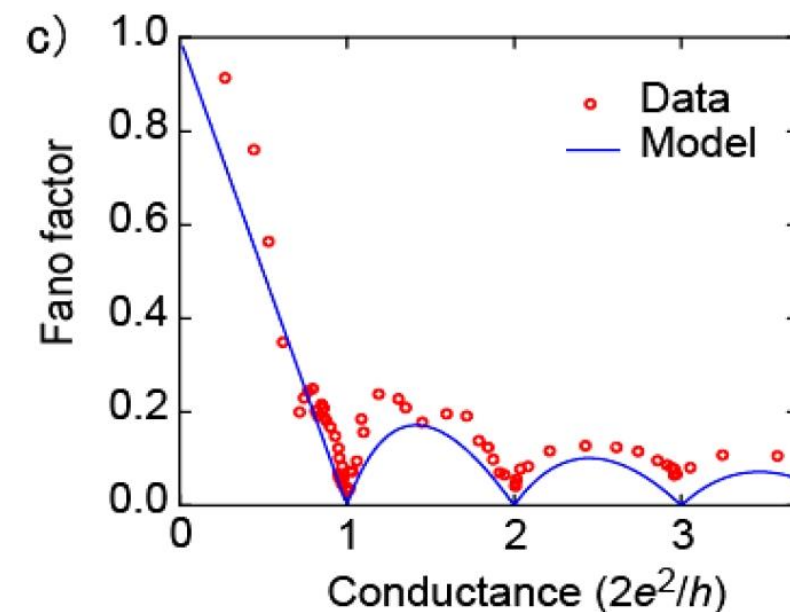
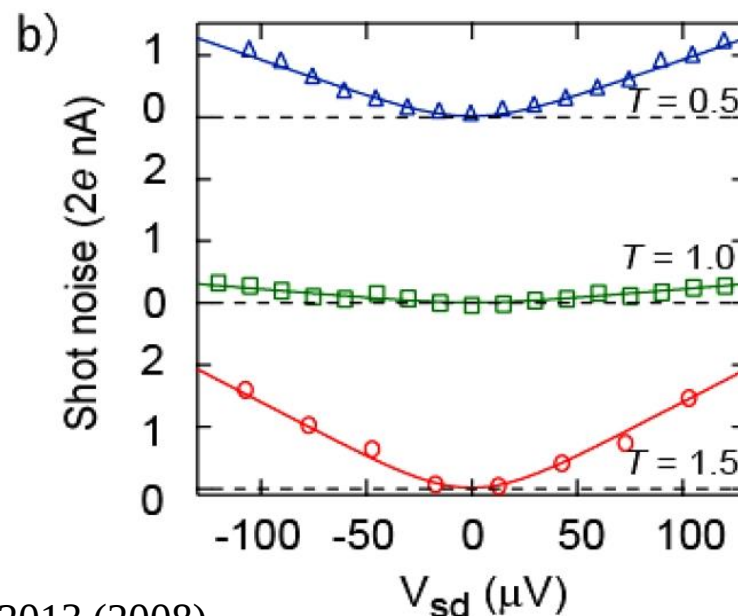
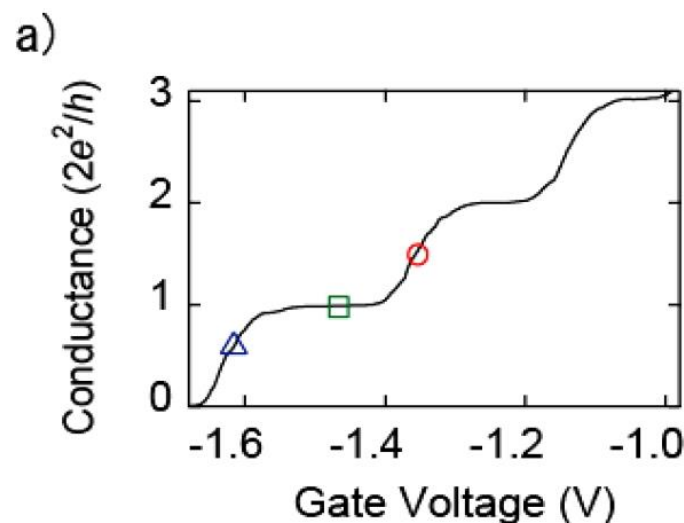
Flow of single electron: Time domain:  $\delta$ -function approximation

$$J_e(t) = e\delta(t - t_0) = e \int_{-\infty}^{\infty} e^{2\pi i f(t-t_0)} df = 2e \int_0^{\infty} \cos[2\pi f(t - t_0)] df$$

Current fluctuation density for infinitesimal band  $df$   $\delta J = d\sqrt{\langle J_e^2 \rangle} = \frac{2e}{\sqrt{2}} df = \sqrt{2}e df$

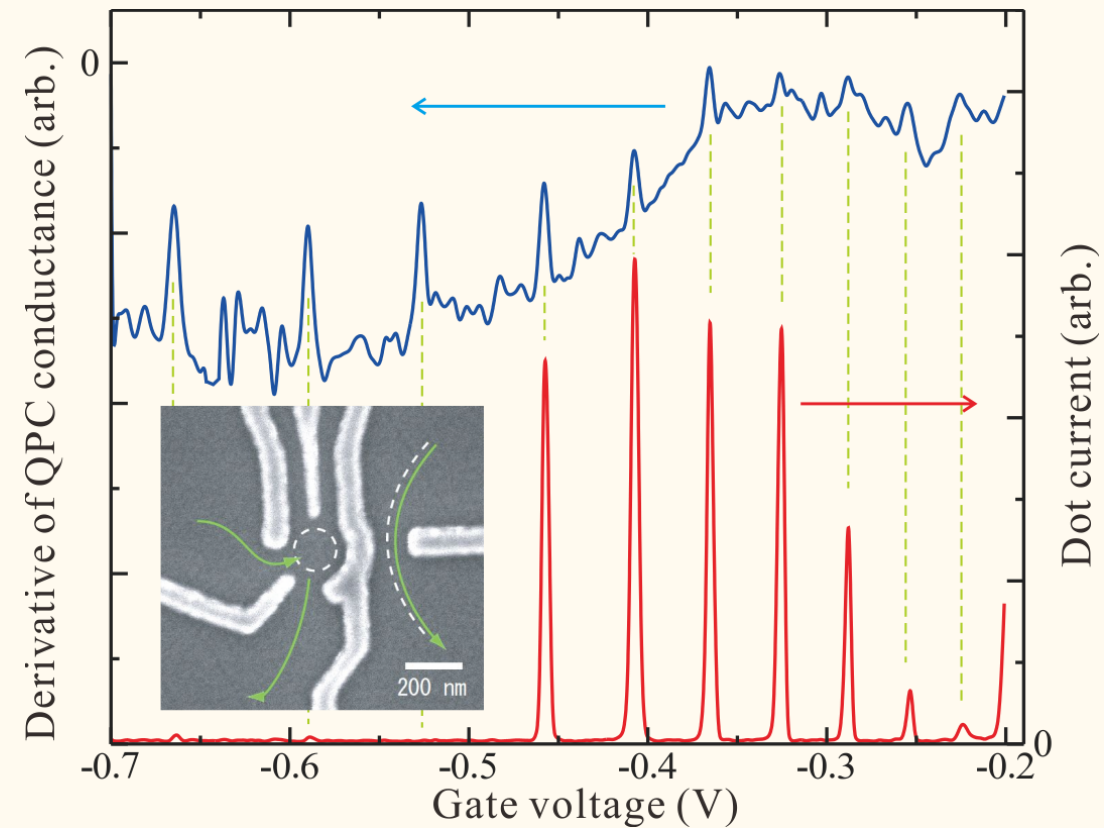
$$\overline{\delta j^2} = (j_p + j_q e^{i\phi})(j_p + j_q e^{-i\phi}) = j_p^2 + j_q^2 + 2j_p j_q \cos \phi = j_p^2 + j_q^2 = 2 \times (\sqrt{2}e)^2 df$$

Flow of  $N$ -electrons  $\overline{\delta J^2} = N \times 2e^2 df = 2e\bar{J}df$  ( $\bar{J} = eN$ ) : Poissonian noise

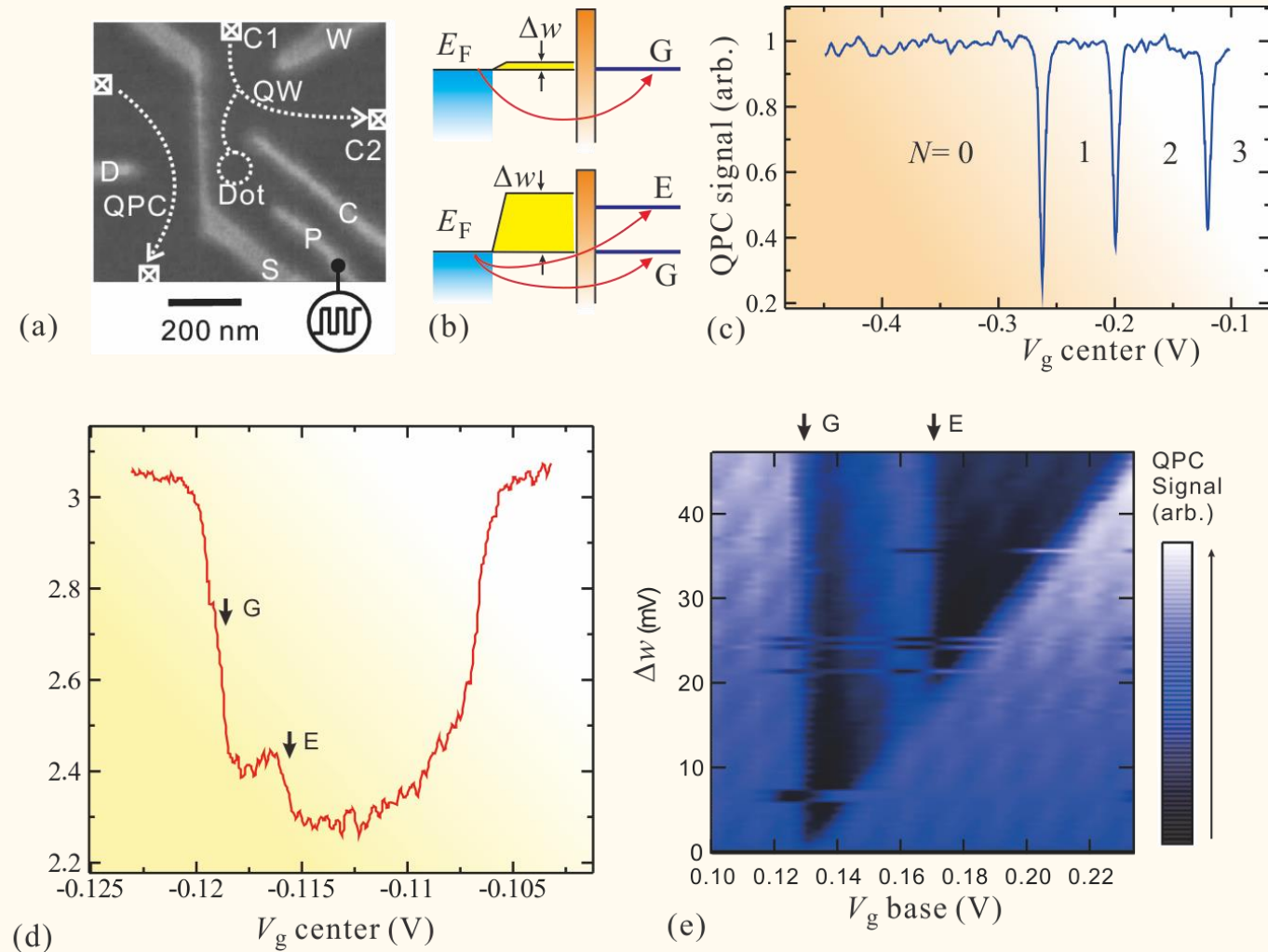


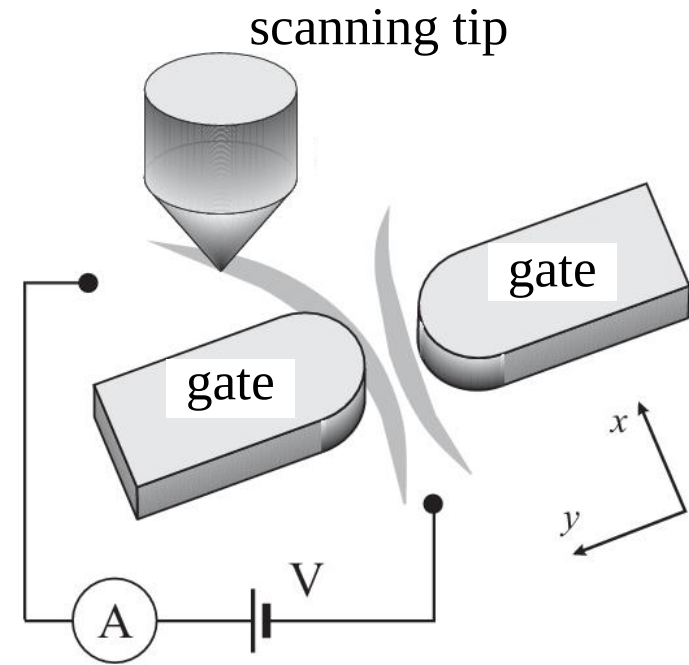
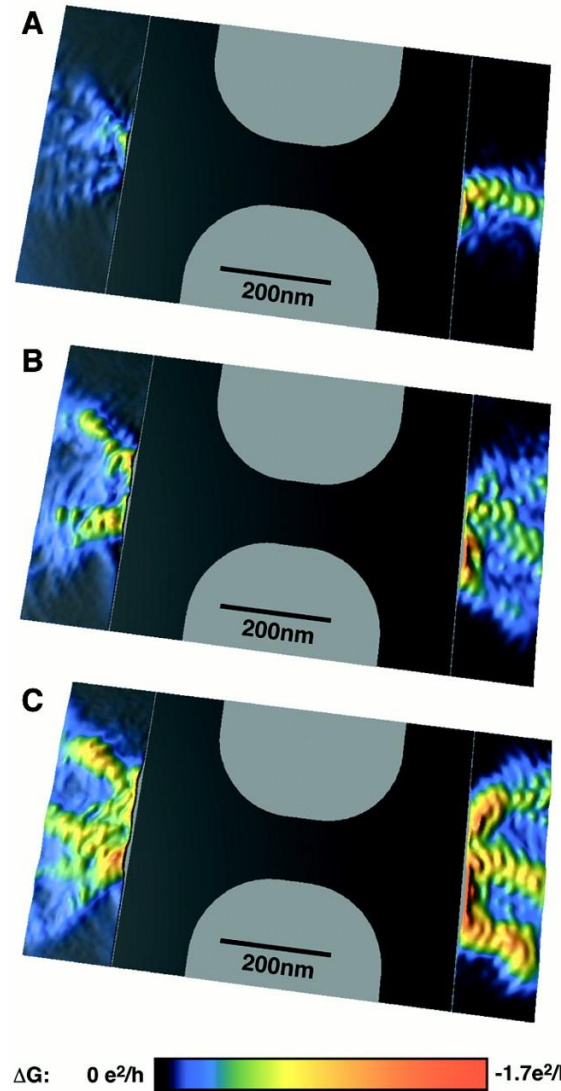
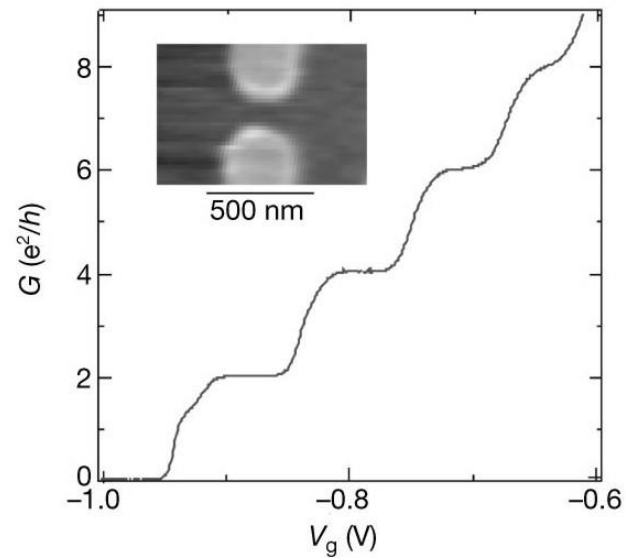
# QPC charge sensor and excited states spectroscopy

## Charge sensor



## Excited states spectroscopy



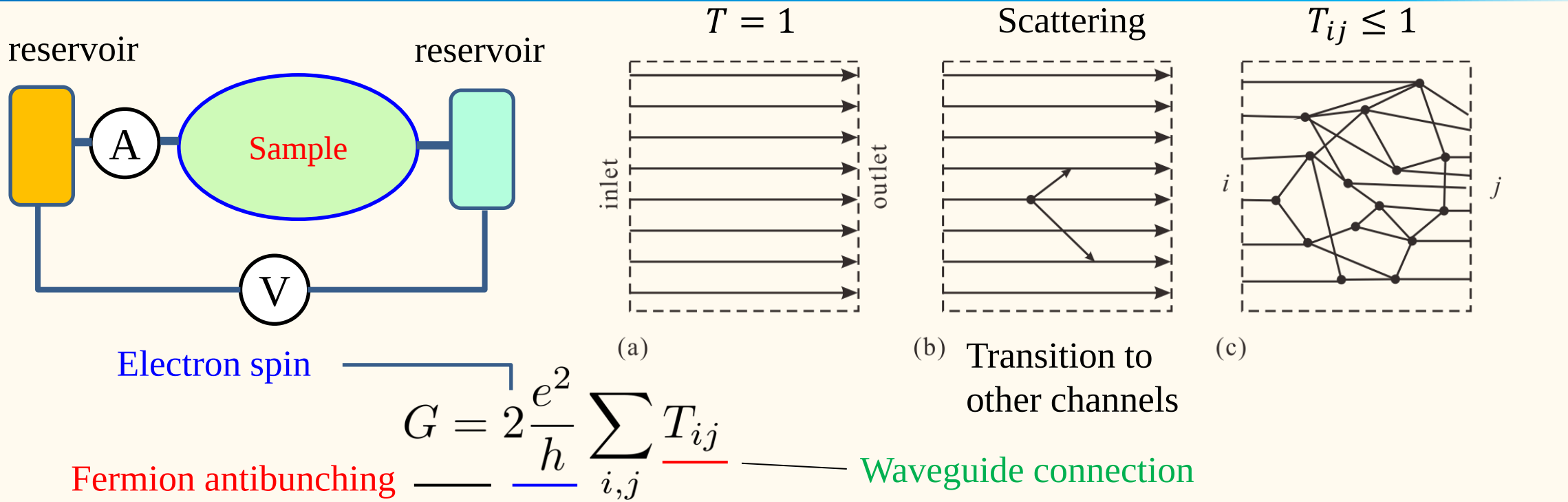


Tip image potential scatters electrons  
 → conductance shifts from quantized value  
 Scattering amplitude  $\propto |\psi|^2$

M. A. Topinka et al.,  
 Nature **410**, 183 (2001)

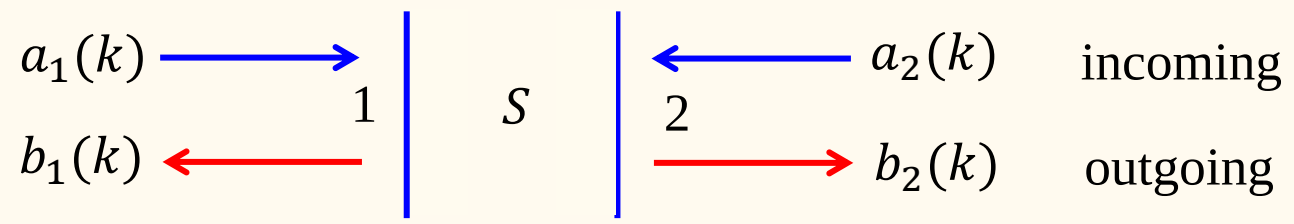
# Landauer formula: multipath, s-matrix

Fundamentals of quantum dots: transport through QD



## Waveguide connection

Scattering matrix S-matrix



$$\begin{pmatrix} b_1(k) \\ b_2(k) \end{pmatrix} = S \begin{pmatrix} a_1(k) \\ a_2(k) \end{pmatrix} = \begin{pmatrix} r_L & t_R \\ t_L & r_R \end{pmatrix} \begin{pmatrix} a_1(k) \\ a_2(k) \end{pmatrix}$$

S-matrices: Unitary

Complex probability density flux  $a_i(k) = \sqrt{v_{Fi}} \psi_{ai}(k_F)$

# T matrix and transport through a quantum dot

$$\begin{pmatrix} b_1(k) \\ b_2(k) \end{pmatrix} = S \begin{pmatrix} a_1(k) \\ a_2(k) \end{pmatrix} = \begin{pmatrix} r_L & t_R \\ t_L & r_R \end{pmatrix} \begin{pmatrix} a_1(k) \\ a_2(k) \end{pmatrix} \quad \text{Transmission, reflection: } \mathcal{T} = |t|^2, \quad \mathcal{R} = |r|^2$$

Conservation of probability  $\mathcal{T} + \mathcal{R} = |t|^2 + |r|^2 = 1$  Subscripts L, R are not shown.

Time reversal symmetry  $\rightarrow t_L = t_R$  Unitary  $\rightarrow r_R = -\frac{t}{t^*} r_L^*$

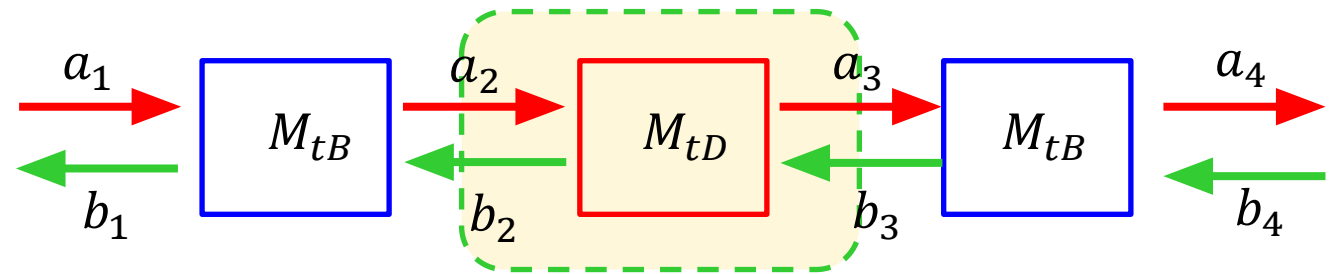
Formally matrix  $\underline{M_t}$  which satisfies  $M_t \begin{pmatrix} a_1 \\ b_1 \end{pmatrix} = \begin{pmatrix} a_2 \\ b_2 \end{pmatrix}$  can be obtained as

T matrix

$$\begin{pmatrix} a_2 \\ b_2 \end{pmatrix} = \begin{pmatrix} 1/t^* & -r^*/t^* \\ -r/t & 1/t \end{pmatrix} \begin{pmatrix} a_1 \\ b_1 \end{pmatrix} \equiv M_t \begin{pmatrix} a_1 \\ b_1 \end{pmatrix}$$

Quantum dot T matrix model

Quantum dot traverse  $\rightarrow$  phase  $kL$



Cascade connection

$\rightarrow$  Product of T-matrices

$$\begin{pmatrix} 1/t^* & -r^*/t^* \\ -r/t & 1/t \end{pmatrix} \begin{pmatrix} \exp(ikL) & 0 \\ 0 & \exp(-ikL) \end{pmatrix} \begin{pmatrix} 1/t^* & -r^*/t^* \\ -r/t & 1/t \end{pmatrix}$$

# Resonant transmission

Total transmission coefficient

$$\mathcal{T}_{\text{tot}}(k) = \frac{1}{1 + 4(|r|^2/|t|^4) \cos^2(\varphi + kL)}, \quad \varphi \equiv \arg(t)$$

Peak position, energy

$$k_n = \frac{(n - 1/2)\pi - \varphi}{L} \equiv \frac{\theta_n}{L}, \quad E'_n = \frac{\hbar^2 k_n^2}{2m} \quad (n = 1, 2, \dots)$$

$$\delta k_n \equiv k - k_n$$

$$4 \frac{|r|^2}{|t|^4} \cos^2(\varphi + kL) \approx 4 \frac{|r|^2}{|t|^4} (L\delta k_n)^2$$

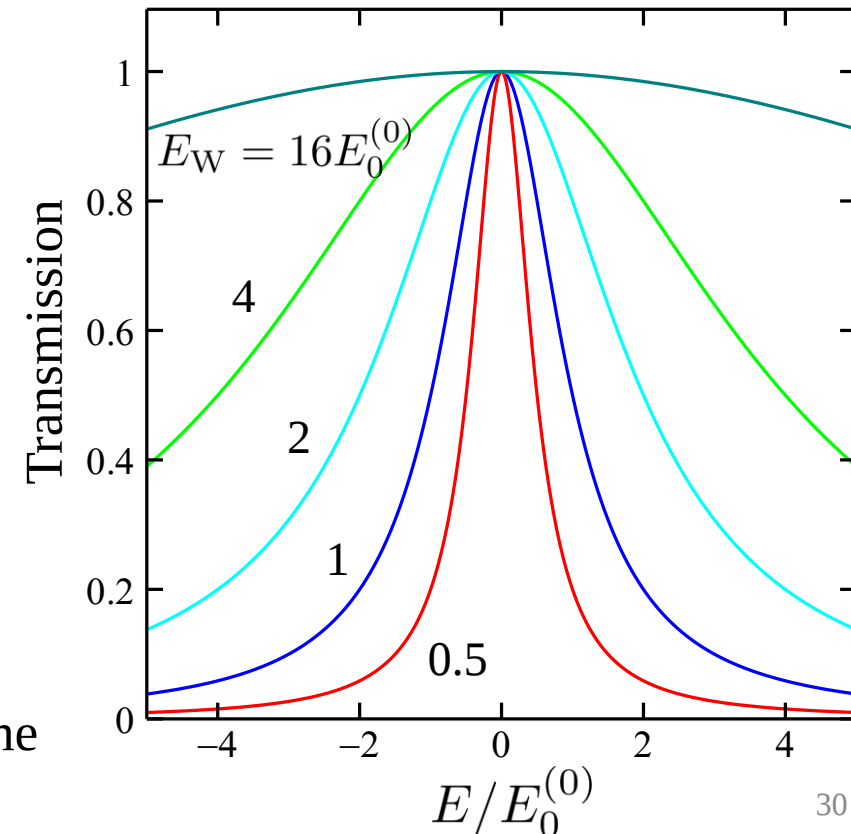
Breit-Wigner or Lorentz form

$$\mathcal{T}_{\text{tot}}^{(n)}(E) = \frac{E_{\text{wn}}^2}{(E - E'_n)^2 + E_{\text{wn}}^2},$$

$$E_{\text{wn}} \equiv \frac{|t|^2}{|r|} \frac{E'_n}{\theta_n}$$

$$2E_{\text{wn}} = \frac{|t|^2}{|r|} \hbar \frac{\hbar k_n}{m} \frac{k_n}{\theta_n} = \frac{|t|^2}{|r|} \hbar \frac{v_n}{L} = \frac{\mathcal{T}}{\sqrt{\mathcal{R}}} \frac{\hbar}{\tau_n}$$

Dot traverse time



# Transport via discrete chemical potential levels

The concept of transmission coefficient is applicable even to finite source-drain voltage transport.

T-matrix method, though, at least needs some modifications.

Occupation numbers of energy levels in the quantum dot:  $\{n_i\} = \{n_1, n_2, \dots\}$

Partition function 
$$Z = \sum_{\{n_i\}} \exp \left[ -\frac{1}{k_B T} \left( \sum_{i=1}^{\infty} E_i n_i + U(N) - N E_F \right) \right] \quad N = \sum_i n_i$$

Distribution function 
$$P(\{n_i\}) = Z^{-1} \exp \left[ -\frac{1}{k_B T} \left( \sum_{i=1}^{\infty} E_i n_i + U(N) - N E_F \right) \right]$$

The joint probability 
$$P_{\text{eq}}(N, n_p = 1) = \sum_{\{n_i\}} P(\{n_i\}) \delta_{N, \sum_i n_i} \delta_{n_p, 1}$$

$$G = \frac{e^2}{k_B T} \sum_{p=1}^{\infty} \sum_{N=1}^{\infty} \frac{\Gamma_p^l \Gamma_p^r}{\Gamma_p^l + \Gamma_p^r} P_{\text{eq}}(N, n_p = 1) [1 - f(E_p + U(N) - U(N-1) - E_F)]$$

# Transport via discrete chemical potential levels (2)

At high temperatures  $\delta E, \frac{e^2}{C} \ll k_B T \ll E_F$   $G = (G_r^{-1} + G_l^{-1})^{-1} = \frac{G_l G_r}{G_l + G_r}$

From the Landauer formula  $G_{l,r} = -\frac{e^2}{h} \int_0^\infty dE \mathcal{T}_{l,r}(E) \frac{df}{dE}$

$$\Gamma_{l,r}(E) = \nu(E) \mathcal{T}_{l,r}(E) = \frac{\mathcal{T}_{l,r}(E)}{h\rho(E)}$$

$$\mathcal{T}_{l,r}(E) = h\Gamma_{l,r}(E)\rho(E)$$

$$G_{l,r} = \frac{e^2}{h} \mathcal{T}_{l,r}(E_F) = e^2 \Gamma_{l,r}(E_F) \rho(E_F)$$

$$G = e^2 \rho \frac{\Gamma_l \Gamma_r}{\Gamma_l + \Gamma_r} = \frac{e^2}{h} \frac{\mathcal{T}_l \mathcal{T}_r}{\mathcal{T}_l + \mathcal{T}_r} \equiv G_\infty$$

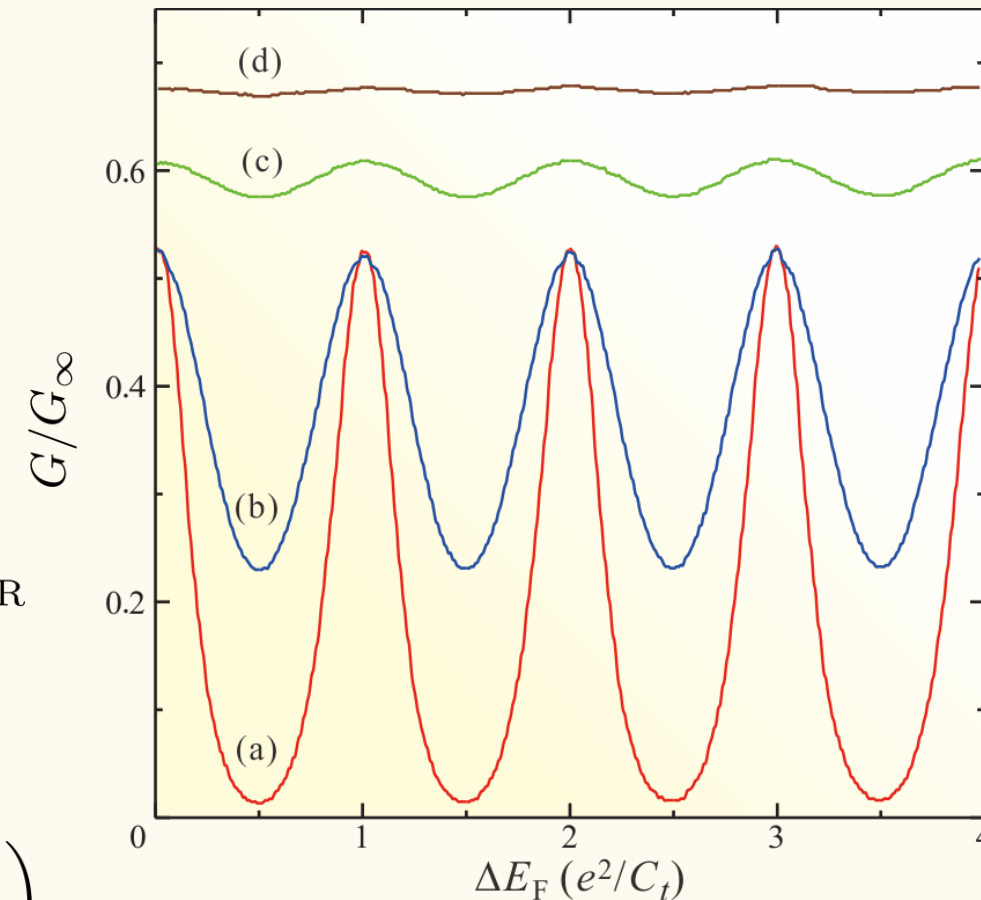
Effective tunnel barrier  $\Delta(N) = U(N) - U(N-1) + \mu_{\text{dot}} - E_R$

$\Delta_{\min} \equiv \Delta(N_{\min})$  (Possible minimum value of  $\Delta$ )

$$\delta E < k_B T < e^2/C$$

$$\frac{G}{G_{\max}} = \frac{(\mu_N - E_F)/k_B T}{\sinh((\mu_N - E_F)/k_B T)} \approx \cosh^{-2} \left( \frac{\mu_N - E_F}{2.5 k_B T} \right)$$

Thermal energy (a)-(d) 0.075, 0.15, 0.3, 0.4 in



# Coulomb peak and temperature sensing

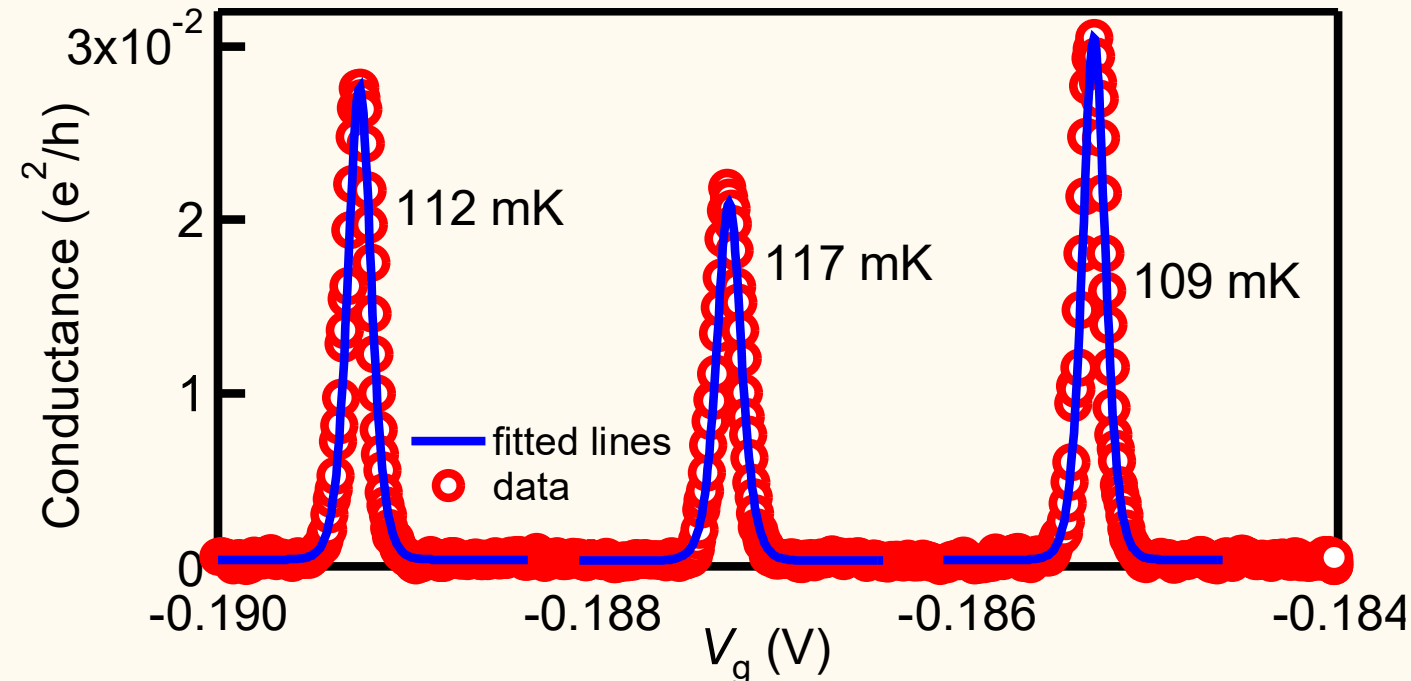
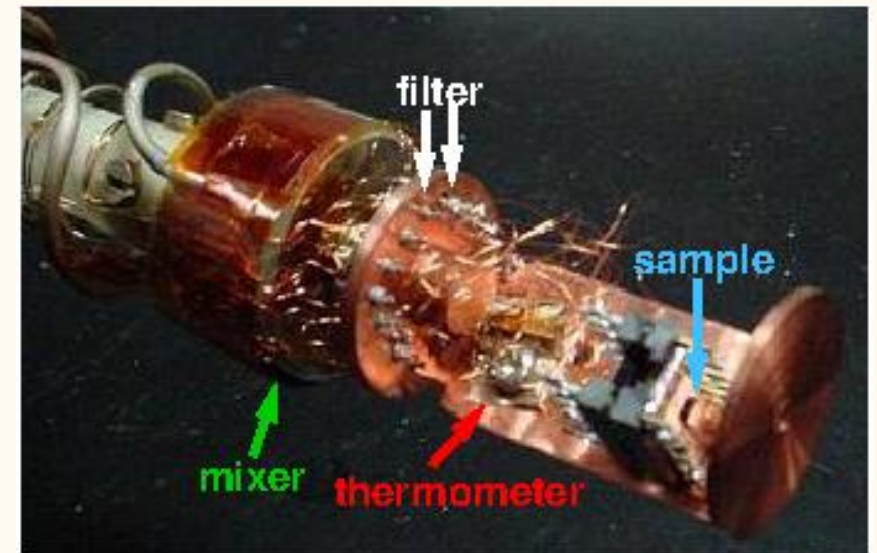
$k_B T \ll \delta E$  incoherent case  $\frac{G}{G_{\max}} = \cosh^{-2} \left( \frac{\mu_0 - E_F}{2k_B T} \right)$

Coherent case  $\mathcal{T}(E) = \frac{(h\Gamma_l)(h\Gamma_r)}{(E - E_0)^2 + (h\Gamma_l)^2 + (h\Gamma_r)^2}$

$$G = -\frac{e^2}{h} \int_0^\infty dE \mathcal{T}(E) \frac{df}{dE}$$

This can be used to measure the electron temperature of the cooled sample.

(Primary thermometry)



# マスター方程式

力学系の状態  $\mathbf{x} = (x_1, x_2, \dots, x_n)$

時間発展が確率論的過程  $\rightarrow x_1, x_2, \dots, x_n$  確率変数

分布関数  $P(\mathbf{x}, t)$

マルコフ (Markov) 過程  $(\mathbf{x}(t_1), \mathbf{x}(t_2), \dots, \mathbf{x}(t_j))$    $t_j$ 以降の  $P(\mathbf{x}, t)$  が決定される  
有限個

(非マルコフ過程：無限個の初期条件を必要とする)

単純マルコフ過程  $\frac{\partial P(\mathbf{x}, t)}{\partial t} = \Gamma[P(\mathbf{x}, t)]$  のように偏微分方程式で表せる

状態遷移  $\mathbf{x} \rightarrow \mathbf{y}$  単位時間当たりの遷移確率  $W(\mathbf{x} \rightarrow \mathbf{y})$  で記述される場合

レート方程式

$$\frac{\partial P(\mathbf{x}, t)}{\partial t} = - \int d\mathbf{y} W(\mathbf{x} \rightarrow \mathbf{y}) P(\mathbf{x}, t) + \int d\mathbf{y} W(\mathbf{y} \rightarrow \mathbf{x}) P(\mathbf{y}, t)$$

マスター方程式 (master equation)

# 量子ドット(単電子効果)伝導とマスター方程式

量子ドット電荷状態指数  $i$ , その確率を  $p_i$     全確率条件  $\sum_i p_i = 1$

$i \rightarrow j$  の遷移確率  $R_{i,j}$      $\frac{dp_i}{dt} = \sum_j R_{i,j} p_j - \sum_j R_{j,i} p_i$     マスター方程式

- 量子ドット電荷状態として基底状態のみ考慮→電子数  $N$  で決まる
- 遷移は隣接電荷状態間のみ

$$\frac{dp_N}{dt} = R_{N,N-1} p_{N-1} + R_{N,N+1} p_{N+1} - (R_{N-1,N} + R_{N+1,N}) p_N$$

遷移確率 (D:ドレイン, S:ソース)  $R_{N,N-1} = f_D(\mu(N), \mu_D) \Gamma_D + f_S(\mu(N), \mu_S) \Gamma_S$

分布関数 ( $\mu(N)$ 位置の空隙確率)  $f_i(\mu(N), \mu_i) = \frac{1}{\exp[(\mu(N) - \mu_i)/k_B T] + 1}, \quad i = D, S$

その他, 同様に

$$\begin{cases} R_{N,N+1} = (1 - f_D(\mu(N+1), \mu_D) \Gamma_D + (1 - f_S(\mu(N+1), \mu_S)) \Gamma_S, \\ R_{N+1,N} = f_D(\mu(N+1), \mu_D) \Gamma_D + f_S(\mu(N+1), \mu_S) \Gamma_S, \\ R_{N-1,N} = (1 - f_D(\mu(N), \mu_D) \Gamma_D + (1 - f_S(\mu(N), \mu_S)) \Gamma_S \end{cases}$$

# 量子ドット伝導とマスター方程式(2)

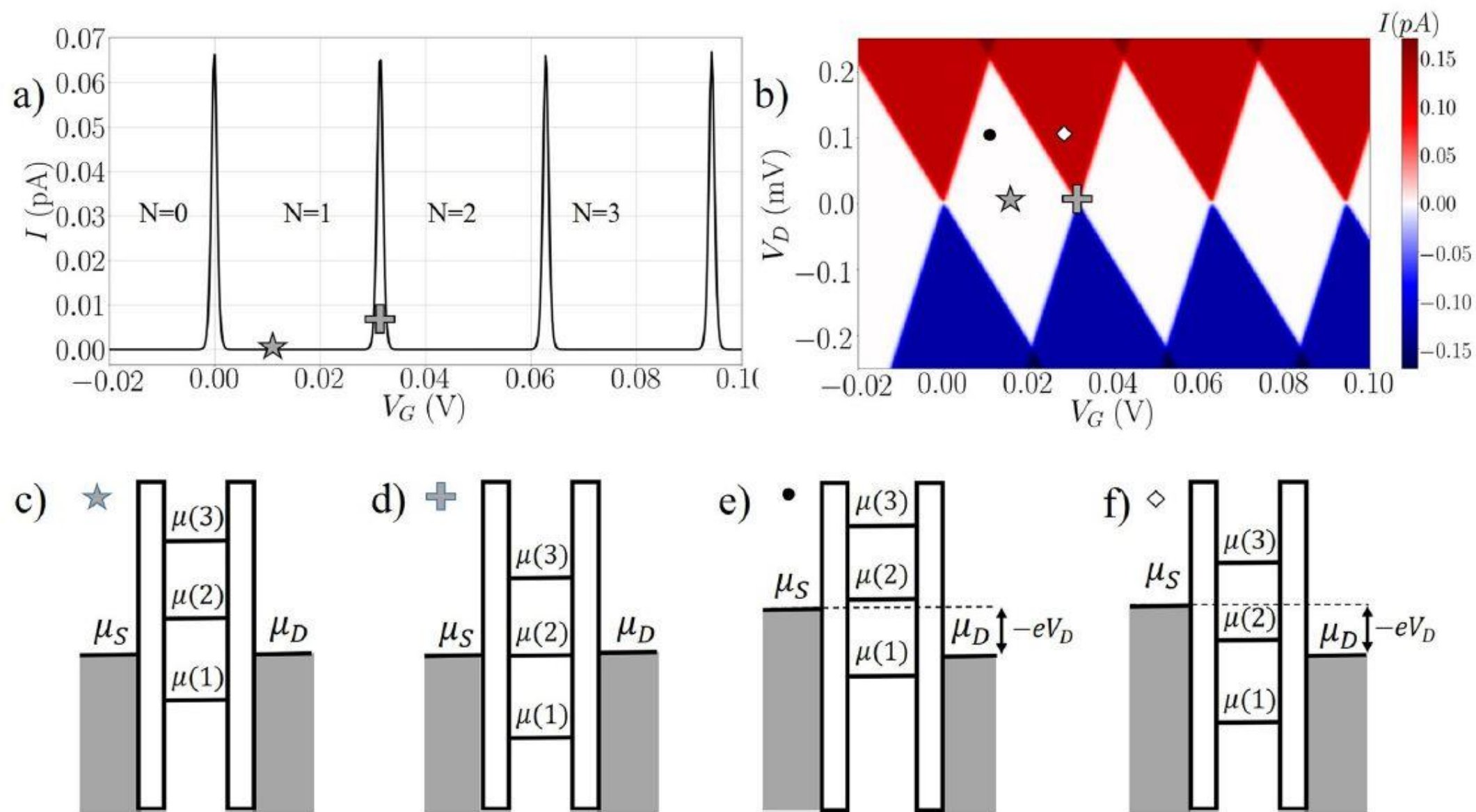
定常状態  $\frac{dp_i}{dt} = R_{i,i-1}p_{i-1} + R_{i,i+1}p_{i+1} - (R_{i-1,i} + R_{i+1,i})p_i = 0 \quad \sum_i p_i = 1$

行列表現  $A = \begin{pmatrix} -R_{1,0} & R_{0,1} & \cdots & R_{0,N} \\ R_{1,0} & -R_{0,1} - R_{2,1} & \cdots & R_{1,N} \\ \vdots & \vdots & \vdots & \vdots \\ R_{N-1,0} & R_{N-1,1} & \cdots & -R_{N-1,N} \\ 1 & 1 & \cdots & 1 \end{pmatrix} \quad C = \begin{pmatrix} 0 \\ 0 \\ \vdots \\ 0 \\ 1 \end{pmatrix} \quad P = \begin{pmatrix} p_0 \\ p_1 \\ \vdots \\ p_N \end{pmatrix}$

Pを数値的に求める  $C = AP, \quad \text{i.e.,} \quad P = A^{-1}C$

電流  $I = -e \left( \sum_i p_i \Gamma_D (1 - f_D(\mu(i), \mu_D)) - \sum_i (1 - p_i) \Gamma_D f_D(\mu(i), \mu_D) \right)$

# 量子ドット伝導とマスター方程式(3)



# Summary

1. 量子ドットとは，量子ドットの製法
2. 単電子効果
3. 量子閉じ込め効果
4. 量子ドットを通した電気伝導